

## ISL6329

Dual PWM Controller Powering AMD SVI Split-Plane Processors

FN7800  
Rev 0.00  
April 19, 2011

The ISL6329 dual PWM controller delivers high efficiency and tight regulation from two synchronous buck DC/DC converters. The ISL6329 supports power control of AMD processors, which operate from a serial VID interface (SVI). The dual output ISL6329 features a multiphase controller to support the Core voltage (VDD) and a single phase controller to power the Northbridge (VDDNB).

A precision core voltage regulation system is provided by a one-to-six-phase PWM voltage regulator (VR) controller. The integration of two power MOSFET drivers adds flexibility in layout and reduces the number of external components in the multi-phase section. A single phase PWM controller with integrated driver provides a second precision voltage regulation system for the Northbridge portion of the processor. This monolithic, dual controller with integrated driver solution provides a cost and space saving power management solution.

For applications that benefit from load line programming to reduce bulk output capacitors, the ISL6329 features temperature compensated output voltage droop. The multiphase portion also includes advanced control loop features for optimal transient response to load application and removal. One of these features is highly accurate, fully differential, continuous DCR current sensing for load line programming and channel current balance. Dual edge modulation is another unique feature, allowing for quicker initial response to high di/dt load transients.

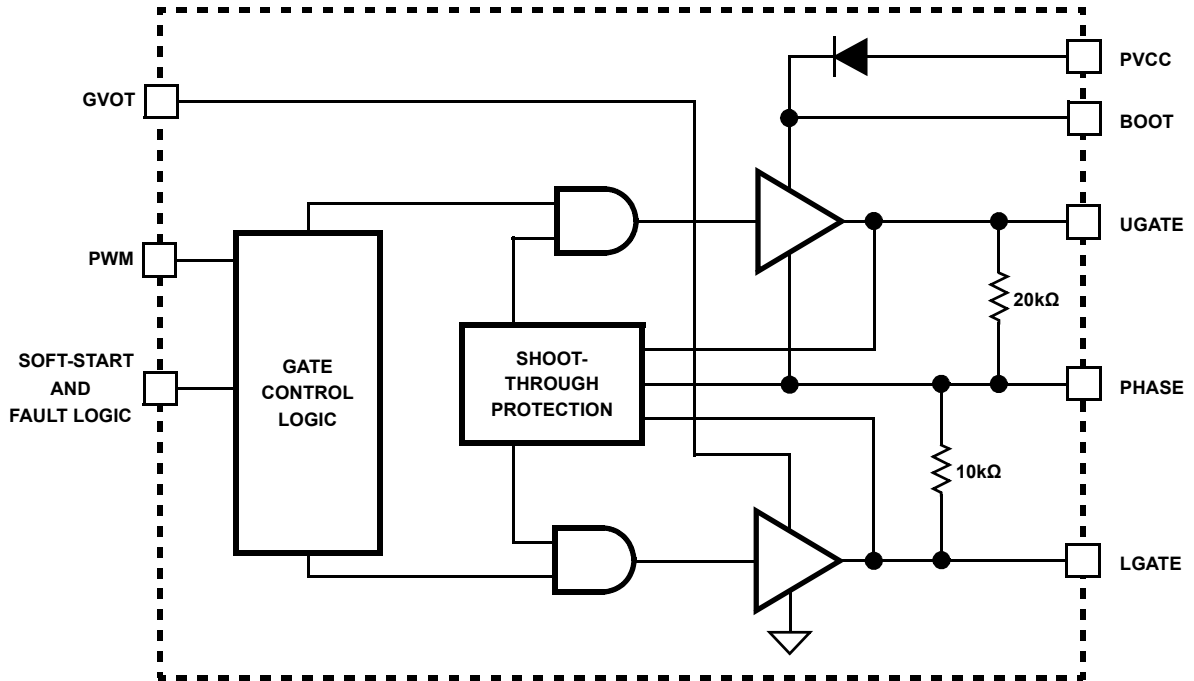
The ISL6329 supports Power Savings Mode by dropping the number of phases to one or two when the PSI\_L bit is set. For even greater power efficiency, diode emulation and gate voltage optimization are implemented in PSI mode.

## Features

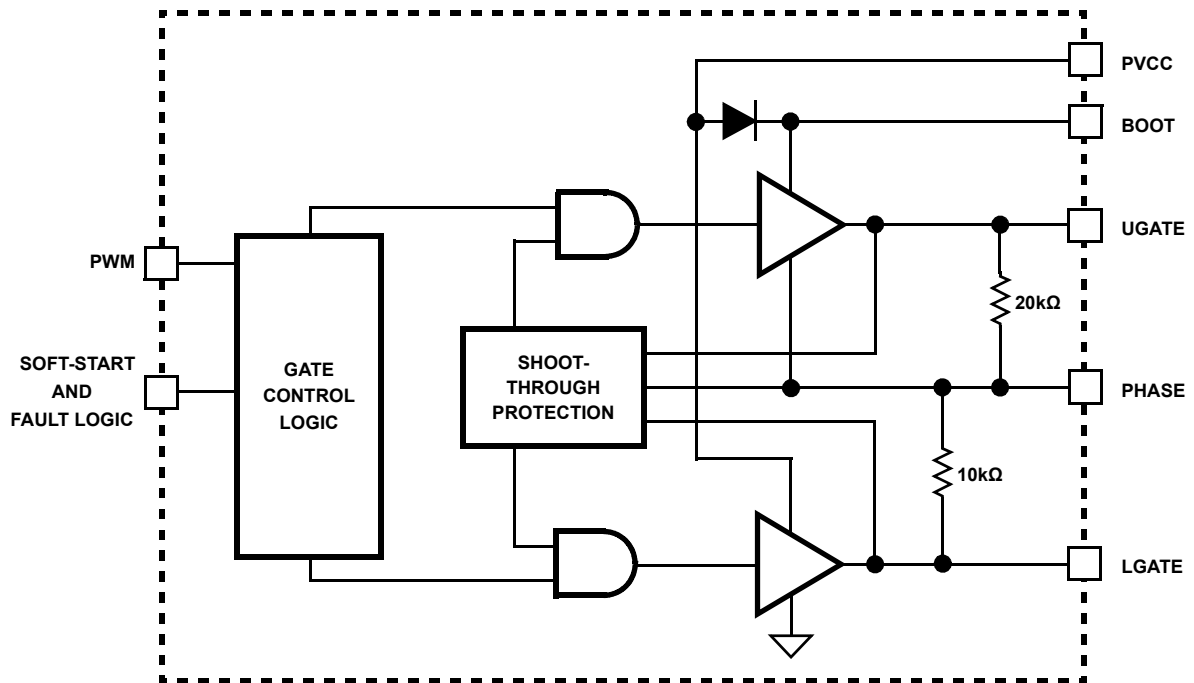
- Processor Core Voltage Via Integrated Multiphase Power Conversion
- Configuration Flexibility
  - 1 or 2-Phase Operation with Internal Drivers
  - 3,4,5 or 6-Phase Operation with External PWM Drivers
- PSI\_L Support
  - Phase Shedding for Improved Efficiency at Light Load
  - Diode Emulation in PSI mode
  - Gate Voltage Optimization
- I<sup>2</sup>C Interface with 8 Selectable Addresses
- Precision Core Voltage Regulation
  - Differential Remote Voltage Sensing
  - ±0.6% System Accuracy Over-Temperature
- Optimal Processor Core Voltage Transient Response
  - Adaptive Phase Alignment (APA)
  - Active Pulse Positioning Modulation
- Fully Differential, Continuous DCR Current Sensing
  - Accurate Load Line Programming
  - Precision Channel Current Balancing
  - Temperature Compensated
- Serial VID Interface Handles up to 3.4MHz Clock Rates
- Two Level Overcurrent Protection Allows for High Current Throttling (I<sub>DD\_SPIKE</sub>)
- Multi-tiered Overvoltage Protection
- Selectable Switching Frequency up to 1MHz
- Simultaneous Digital Soft-Start of Both Outputs
- Pb-Free (RoHS Compliant)

# Integrated Driver Block Diagram

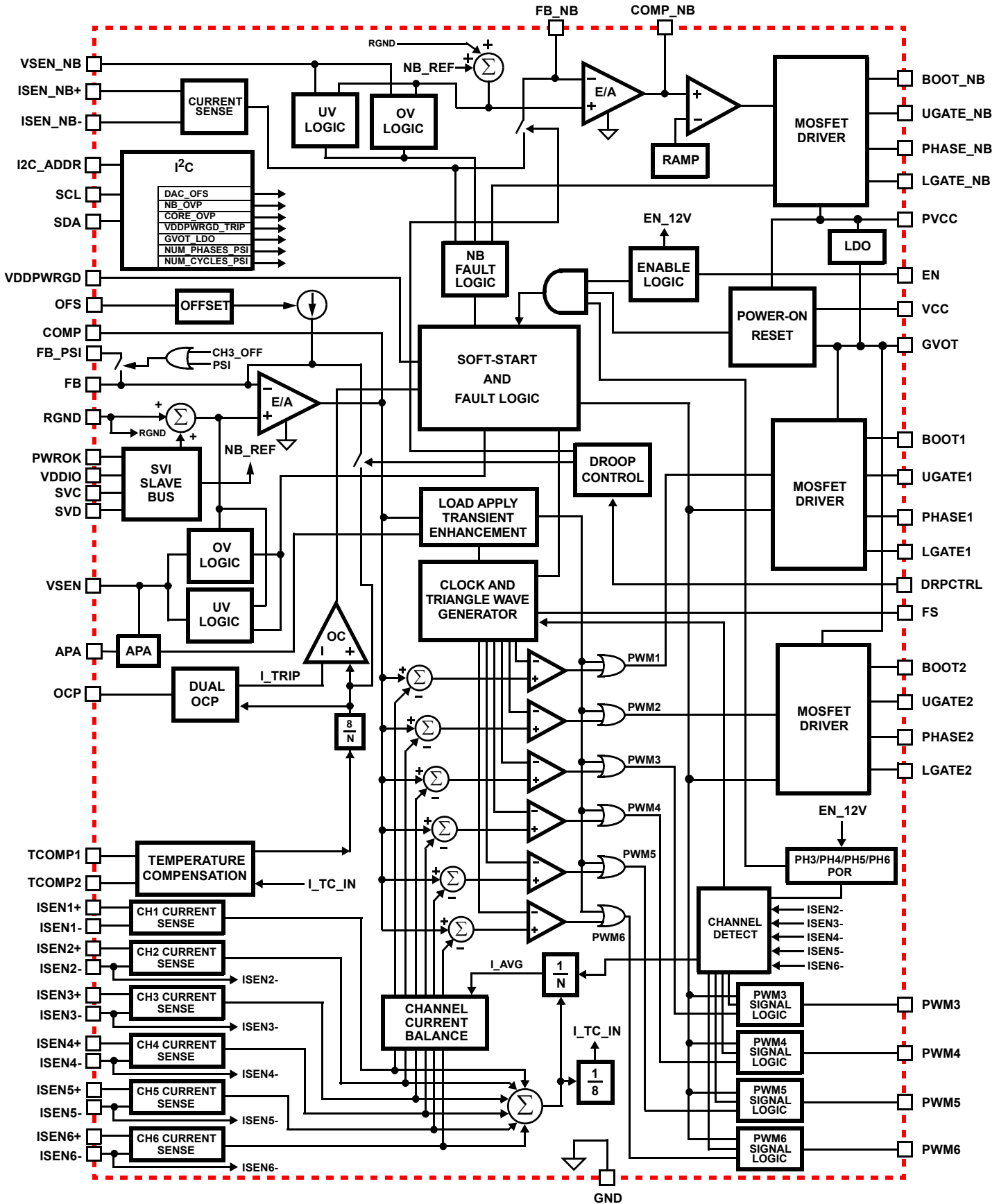
## Channels 1 and 2 Gate Drive



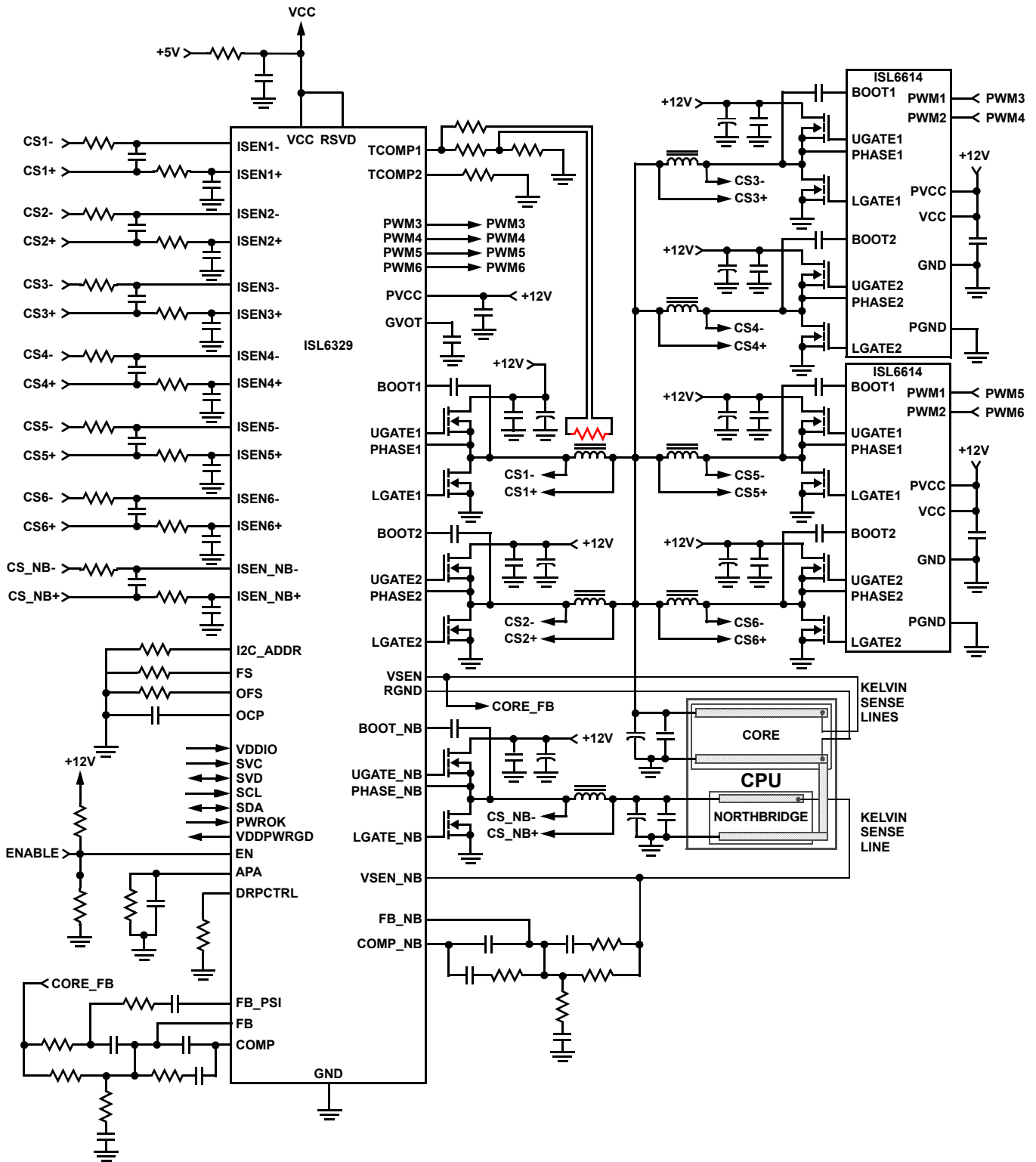
## Northbridge Gate Drive



# Controller Block Diagram

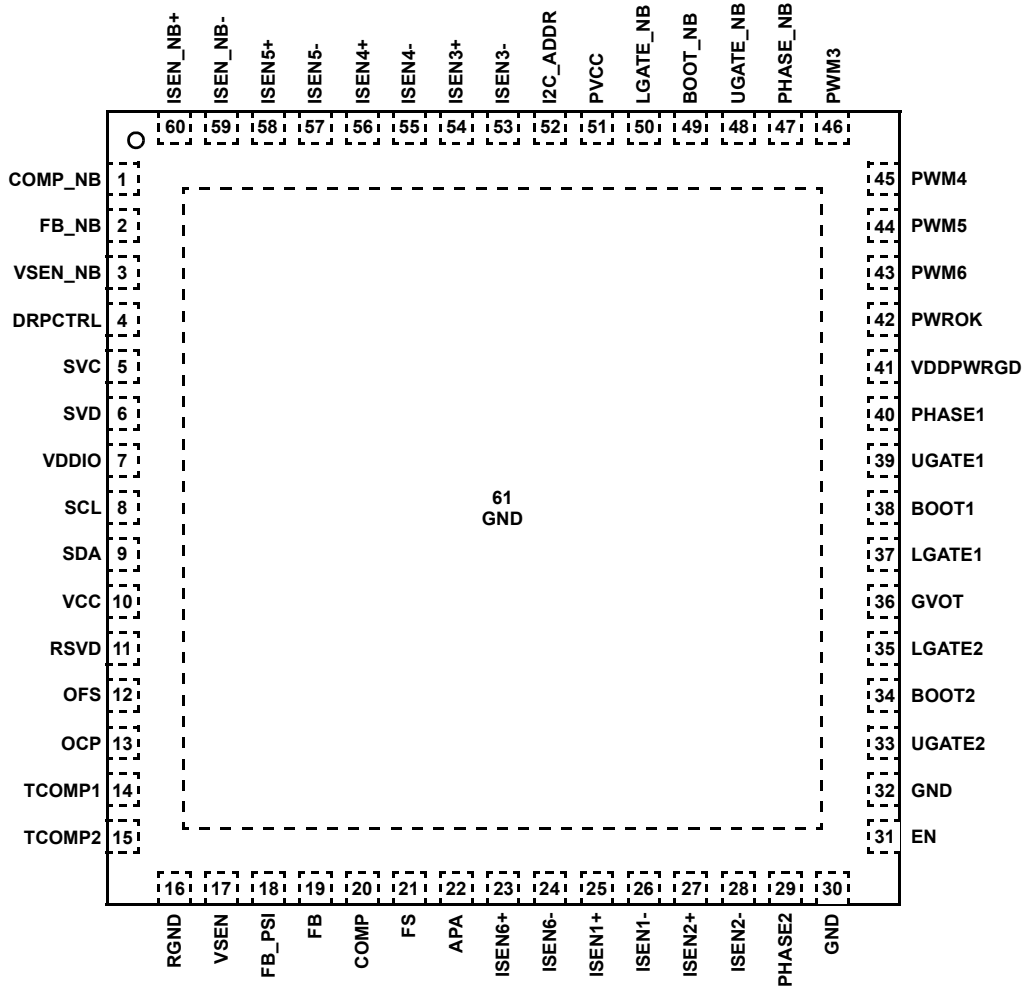


# Typical Application



# Pin Configuration

ISL6329  
(60 LD QFN)  
TOP VIEW



## Functional Pin Descriptions

PIN NAME	PIN NUMBER	DESCRIPTION
COMP_NB	1	Output of the internal error amplifier for the Northbridge regulator.
FB_NB	2	Inverting input to the internal error amplifier for the Northbridge regulator.
VSEN_NB	3	Non-inverting input to the Northbridge regulator precision differential remote-sense amplifier. This pin should be connected to the remote Northbridge sense pin of the processor, VDDNB_SENSE.
DRPCTRL	4	Droop Control for Core and Northbridge. This pin is used to set up one of four user programmable selections via a resistor tied to ground: Core Droop On and Northbridge Droop On; Core Droop Off and Northbridge Droop On, Core Droop On and Northbridge Droop Off; Core Droop Off and Northbridge Droop Off.
SVC	5	Serial VID clock input from the AMD processor.
SVD	6	Serial VID data bi-directional signal to and from the master device on AMD processor.
VDDIO	7	Reference voltage for the SVI communication bus. Connect this pin to the system VDDIO and decouple using a quality 0.1µF ceramic capacitor.
SCL	8	Connect this pin to the clock signal for the I <sup>2</sup> C bus, which is a logic level input signal. The clock signal tells the controller when data is available on the I <sup>2</sup> C bus.

## Functional Pin Descriptions (Continued)

PIN NAME	PIN NUMBER	DESCRIPTION
SDA	9	Connect this pin to the bidirectional data line of the I <sup>2</sup> C bus, which is a logic level input/output signal. All I <sup>2</sup> C data is sent over this line, including the address of the device the bus is trying to communicate with and what functions the device should perform.
VCC	10	VCC is the bias supply for the ICs small-signal circuitry. Connect this pin to a +5V supply and decouple using a quality 0.1µF ceramic capacitor.
RSVD	11	RESERVED. Connect this pin directly to the VCC pin.
OFS	12	The OFS pin provides a means to program a DC current for generating an offset voltage across the resistor between FB and VSEN. The offset current is generated via an external resistor and precision internal voltage references. The polarity of the offset is selected by connecting the resistor to GND or VCC. For no offset, the OFS pin should be left unconnected.
OCF	13	A capacitor from this pin to ground determines the time that the regulator is allowed to service a load current spike that exceeds the internal OCF trip point.
TCOMP1, TCOMP2	14, 15	These two pins are used to compensate the inductor current sensing for fluctuations due to temperature.
RGND	16	Inverting input to the Core and Northbridge regulator precision differential remote-sense amplifiers. This pin should be connected to the remote ground sense pin of the processor core, VSS_SENSE.
VSEN	17	Non-inverting input to the Core regulator precision differential remote-sense amplifier. This pin should be connected to the remote Core sense pin of the processor, VDD_SENSE.
FB_PSI	18	In PSI mode this pin is internally shorted to the FB pin to augment the feedback compensation network for the lower phase count.
FB	19	Inverting input to the internal error amplifier for the Core regulator.
COMP	20	Output of the internal error amplifier for the Core regulator.
FS	21	This is a dual function pin. A resistor, placed from FS to either Ground or VCC sets the switching frequency of both controllers. Refer to Equation 1 for proper resistor calculation. $R_T = 10^{[10.61 - 1.035 \log(f_s)]} \quad (\text{EQ. 1})$ If the resistor is tied to ground, the number of active phases in PSI mode is 1. If the resistor is tied to VCC, the number of active phases in PSI mode is 2.
APA	22	Allows for programming of the Auto Phase Alignment threshold. A resistor in parallel with a capacitor to ground is used to set this threshold.
ISENn+, ISENn-, ISEN_NB+, ISEN_NB-	23, 24, 25, 26, 27, 28, 53, 54, 55, 56, 57, 58, 59, 60	These pins are used for differentially sensing the corresponding channel output currents. The sensed currents are used for channel balancing, protection, and core load line regulation. Connect ISEN- to the node between the RC sense elements surrounding the inductor of the respective channel. Tie the ISEN+ pin to the other end of the sense capacitor through a resistor, R <sub>ISEN</sub> . The voltage across the sense capacitor is proportional to the inductor current. The sense current, therefore, is proportional to the inductor current and scaled by the DCR of the inductor and R <sub>ISEN</sub> .
PHASE1, PHASE2	40, 29	Connect these pins to the sources of the corresponding upper MOSFETs. These pins are the return path for the upper MOSFET drives.
GND	30, 32, 61	Bias and reference ground for the IC. The GND connection for the ISL6329 is made with three pins and through the thermal pad on the bottom of the package.
EN	31	This pin is a threshold-sensitive (approximately 0.85V) system enable input for the controller. Held low, this pin disables both CORE and NB controller operation. Pulled high, the pin enables both controllers for operation. A second function of this pin is to provide driver bias monitor for external drivers. A resistor divider with the center tap connected to this pin from the drive bias supply prevents enabling the controller before insufficient bias is provided to external driver. The resistors should be selected such that when the POR-trip point of the external driver is reached, the voltage at this pin meets the above mentioned threshold level.
UGATE1, UGATE2	39, 33	Connect this pin to the corresponding upper MOSFET gate. This pin provides the PWM-controlled gate drive for the upper MOSFET and is monitored for shoot-through prevention purposes.

## Functional Pin Descriptions (Continued)

PIN NAME	PIN NUMBER	DESCRIPTION
BOOT1, BOOT2	38, 34	This pin provides the bias voltage for the corresponding upper MOSFET drive. Connect this pin to appropriately-chosen external bootstrap capacitor. The internal bootstrap diode connected to the PVCC pin provides the necessary bootstrap charge.
LGATE1, LGATE2	37, 35	Connect this pin to the corresponding MOSFET's gate. This pin provides the PWM-controlled gate drive for the lower MOSFET. This pin is also monitored by the adaptive shoot-through protection circuitry to determine when the lower MOSFET has turned off.
GVOT	36	The power supply pin for the multiphase internal MOSFET drivers. In normal operation, this pin is shorted to the PVCC pin. While in PSI mode, this pin is tied to the output of the internal LDO for Gate Drive Voltage Optimization. Decouple this pin with a quality 2.2 $\mu$ F ceramic capacitor.
VDDPWRGD	41	During normal operation, this pin indicates whether both output voltages are within specified overvoltage and undervoltage limits. If either output voltage exceeds these limits or a reset event occurs (such as an overcurrent event), the pin is pulled low. This pin is always low prior to the end of soft-start.
PWROK	42	System wide Power Good input signal. If this pin is low, the two SVI bits are decoded to determine the "metal VID". When pin is high, the SVI is actively running its protocol.
PWM3, PWM4, PWM5, PWM6	46, 45, 44, 43	Pulse-width modulation outputs. Connect these pins to the PWM input pins of an Intersil driver IC if 3, 4, 5, or 6-phase operation is desired. Connect the ISEN- pins of the channels not desired to +5V to disable them. Channels must be disabled in decremental order.
PHASE_NB	47	Connect this pin to the source of the corresponding upper MOSFET. This pin is the return path for the upper MOSFET drive. This pin is used to monitor the voltage drop across the upper MOSFET for overcurrent protection.
UGATE_NB	48	Connect this pin to the corresponding upper MOSFET gate. This pin provides the PWM-controlled gate drive for the upper MOSFET and is monitored for shoot-through prevention purposes.
BOOT_NB	49	This pin provides the bias voltage for the corresponding upper MOSFET drive. Connect this pin to appropriately-chosen external bootstrap capacitor. The internal bootstrap diode connected to the PVCC pin provides the necessary bootstrap charge.
LGATE_NB	50	Connect this pin to the corresponding MOSFET's gate. This pin provides the PWM-controlled gate drive for the lower MOSFET. This pin is also monitored by the adaptive shoot-through protection circuitry to determine when the lower MOSFET has turned off.
PVCC	51	The power supply pin for the internal MOSFET drivers. Connect this pin to +12V. This pin is the input to the internal LDO for GVOT. Decouple this pin with a quality 1.0 $\mu$ F ceramic capacitor.
I2C_ADDR	52	A resistor tied from this pin to either ground or VCC will set the I <sup>2</sup> C address. There are eight I <sup>2</sup> C programmable addresses.

## Ordering Information

PART NUMBER (Notes 1, 2, 3)	PART MARKING	TEMP. (°C)	PACKAGE (Pb-free)	PKG. DWG. #
ISL6329CRZ	ISL6329 CRZ	0 to +70	60 Ld 7x7 QFN	L60.7x7
ISL6329IRZ	ISL6329 IRZ	-40 to +85	60 Ld 7x7 QFN	L60.7x7

### NOTES:

1. Add "-T\*" suffix for tape and reel. Please refer to TB347 for details on reel specifications.
2. These Intersil Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matte tin plate plus anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
3. For Moisture Sensitivity Level (MSL), please see device information page for [ISL6329](#). For more information on MSL please see techbrief [TB363](#).

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## Absolute Maximum Ratings

Supply Voltage (VCC)	-0.3V to +6.5V
Supply Voltage (PVCC)	-0.3V to +15V
Absolute Boot Voltage (V <sub>BOOT</sub> )	GND - 0.3V to GND + 36V
Phase Voltage (V <sub>PHASE</sub> )	GND - 0.3V to 30V
(PVCC = 12V) GND - 8V (<400ns, 20μJ) to 31V (<200ns, 20μJ, V <sub>BOOT-PHASE</sub> = 5V)	
Upper Gate Voltage (V <sub>UGATE</sub> )	V <sub>PHASE</sub> - 0.3V to V <sub>BOOT</sub> + 0.3V
	V <sub>PHASE</sub> - 3.5V (<100ns Pulse Width, 2μJ) to V <sub>BOOT</sub> + 0.3V
Lower Gate Voltage (V <sub>LGATE</sub> )	GND - 0.3V to PVCC + 0.3V
	GND - 5V (<100ns Pulse Width, 2μJ) to PVCC + 0.3V
Input, Output, or I/O Voltage	GND - 0.3V to VCC + 0.3V
ESD Rating	
Human Body Model (Tested per JESD22-A114F)	2000V
Machine Model (Tested per JESD22-A115C)	200V
Charged Device Model (Tested per JESD22-C101D)	2000V
Latch Up (Tested per JESD78C; Class II, Level A)	100mA

## Thermal Information

Thermal Resistance	$\theta_{JA}$ (°C/W)	$\theta_{JC}$ (°C/W)
QFN Package (Notes 4, 5)	25	1
Maximum Junction Temperature	+150°C	
Maximum Storage Temperature Range	-65°C to +150°C	
Pb-Free Reflow Profile	see link below	
	<a href="http://www.intersil.com/pbfree/Pb-FreeReflow.asp">http://www.intersil.com/pbfree/Pb-FreeReflow.asp</a>	

## Recommended Operating Conditions

VCC Supply Voltage	+5V ±5%
PVCC Supply Voltage	+5V to 12V ±5%
Ambient Temperature (ISL6329CRZ)	0°C to +70°C
Ambient Temperature (ISL6329IRZ)	-40°C to +85°C

**CAUTION:** Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

### NOTES:

- $\theta_{JA}$  is measured in free air with the component mounted on a high effective thermal conductivity test board with "direct attach" features. See Tech Brief TB379.
- For  $\theta_{JC}$ , the "case temp" location is the center of the exposed metal pad on the package underside.

## Electrical Specifications **Boldface limits apply over the operating temperature range.**

PARAMETER	TEST CONDITIONS	MIN (Note 7)	TYP	MAX (Note 7)	UNITS
<b>BIAS SUPPLIES</b>					
Input Bias Supply Current	I <sub>VCC</sub> ; EN = high		26	<b>35</b>	mA
Gate Drive Bias Current - PVCC Pin	I <sub>PVCC</sub> ; EN = high		4	<b>8</b>	mA
VCC POR (Power-On Reset) Threshold	VCC Rising		4.35	<b>4.7</b>	V
	VCC Falling	<b>3.6</b>	3.85		V
PVCC POR (Power-On Reset) Threshold	PVCC Rising		4.45	<b>4.7</b>	V
	PVCC Falling	<b>3.6</b>	3.75		V
GVOT POR (Power-On Reset) Threshold	GVOT Rising		4.45	<b>4.7</b>	V
	GVOT Falling	<b>3.6</b>	3.75		V
<b>PWM MODULATOR</b>					
Oscillator Frequency Accuracy, F <sub>SW</sub>	R <sub>T</sub> = 100kΩ to Ground	<b>230</b>	250	<b>265</b>	kHz
Oscillator Frequency Accuracy, F <sub>SW</sub>	R <sub>T</sub> = 100kΩ to VCC	<b>225</b>	255	<b>287</b>	kHz
Typical Adjustment Range of Switching Frequency	(Note 6)	<b>0.150</b>		<b>1.5</b>	MHz
Oscillator Ramp Amplitude, V <sub>PP</sub>	(Note 6)		1.5		V
<b>CONTROL THRESHOLDS</b>					
EN Rising Threshold		<b>0.8</b>	0.87	<b>0.92</b>	V
EN Hysteresis		<b>70</b>	100	<b>190</b>	mV
PWROK Input HIGH Threshold		<b>0.9</b>	1.05	<b>1.2</b>	V
PWROK Input LOW Threshold		<b>0.8</b>	0.95	<b>1.1</b>	V
VDDPWRGD	Open drain, VDDPWRGD = 1.24kΩ to 5V			<b>0.5</b>	V
PWM Channel Disable Threshold	V <sub>ISEN2</sub> , V <sub>ISEN3</sub> , V <sub>ISEN4</sub> , V <sub>ISEN5</sub> , V <sub>ISEN6</sub>			<b>4.4</b>	V

**Electrical Specifications** Boldface limits apply over the operating temperature range. (Continued)

PARAMETER	TEST CONDITIONS	MIN (Note 7)	TYP	MAX (Note 7)	UNITS
<b>PIN ADJUSTABLE OFFSET</b>					
OFS Reference Voltage Accuracy (Positive Offset)		<b>0.29</b>		<b>0.32</b>	V
OFS Reference Voltage Accuracy (Negative Offset)		<b>VCC-1.7</b>		<b>VCC-1.56</b>	V
<b>REFERENCE AND DAC</b>					
System Accuracy (VDAC > 1.000V)		<b>-0.6</b>		<b>+0.6</b>	%
System Accuracy (0.600V < VDAC < 1.000V)		<b>-1.0</b>		<b>+1.0</b>	%
System Accuracy (VDAC < 0.600V)		<b>-2.0</b>		<b>+2.0</b>	%
<b>GATE VOLTAGE OPTIMIZATION</b>					
GVOT Voltage	PVCC = 12V, GVOT = 5.75V, I <sub>GVOT</sub> = 50mA		5.75		V
	PVCC = 12V, GVOT = 6.75V, I <sub>GVOT</sub> = 50mA		6.75		V
	PVCC = 12V, GVOT = 7.75V, I <sub>GVOT</sub> = 50mA		7.75		V
	PSI_L = 1, I <sub>GVOT</sub> = 50mA		<b>11.1</b>		V
<b>ERROR AMPLIFIER</b>					
DC Gain	R <sub>L</sub> = 10k to ground, (Note 6)		96		dB
Gain-Bandwidth Product	C <sub>L</sub> = 100pF, R <sub>L</sub> = 10k to ground, (Note 6)		20		MHz
Slew Rate	C <sub>L</sub> = 100pF, Load = ±400μA, (Note 6)		8		V/μs
Maximum Output Voltage	Load = 500μA	<b>3.8</b>	4.2		V
Minimum Output Voltage	Load = -500μA		1.4	<b>1.65</b>	V
FB_PSI Impedance	Impedance Between FB and FB_PSI		60		Ω
<b>OUTPUT RAMP RATE</b>					
Soft-Start Slew Rate (SR <sub>SS</sub> ) And VID-On-The-Fly Slew Rate (SR <sub>VOP</sub> )	I <sup>2</sup> C Default Slew Rate	<b>2.5</b>	3	<b>3.8</b>	mV/μs
<b>PWM OUTPUTS</b>					
PWM Output Voltage LOW	I <sub>LOAD</sub> = ±500μA			<b>0.35</b>	V
PWM Output Voltage HIGH	I <sub>LOAD</sub> = ±500μA	<b>4.0</b>			V
PWM Tri-State Output Voltage	I <sub>LOAD</sub> = 100μA	<b>1.5</b>	2	<b>2.7</b>	V
<b>DROOP CURRENT</b>					
Core Tolerance	6 Phases Active, R <sub>ISENn</sub> = 100Ω, I <sub>ISENn</sub> = 80μA	<b>67</b>	75	<b>83</b>	μA
Northbridge Tolerance	R <sub>ISEN_NB</sub> = 100Ω, I <sub>ISEN_NB</sub> = 100μA	<b>67</b>	75	<b>83</b>	μA
<b>CORE OVERCURRENT PROTECTION</b>					
Instant Overcurrent Trip Level - I <sub>DRDROOP</sub>		<b>120</b>	145	<b>165</b>	μA
Instant Overcurrent Trip Level - I <sub>SEN_AVG</sub>		<b>134</b>	155	<b>180</b>	μA
Delayed Overcurrent Trip Level - I <sub>SEN_AVG</sub>	(Note 6)		100		μA
Overcurrent Trip Level - Individual Channel	(Note 6)		170		μA
OCP Pin Current	Delayed OCP Level Tripped		20		μA
OCP Pin Voltage Trip	Delayed OCP Level Tripped	<b>1.95</b>	2.05	<b>2.15</b>	V
<b>NORTH BRIDGE OVERCURRENT PROTECTION</b>					
Overcurrent Trip Level - I <sub>SEN_NB</sub>		<b>85</b>		<b>137</b>	μA
Overcurrent Trip Level - I <sub>DRDROOP_NB</sub>	ISL6329CRZ	<b>80</b>		<b>128</b>	μA
Overcurrent Trip Level - I <sub>DRDROOP_NB</sub>	ISL6329IRZ	<b>76</b>		<b>128</b>	μA

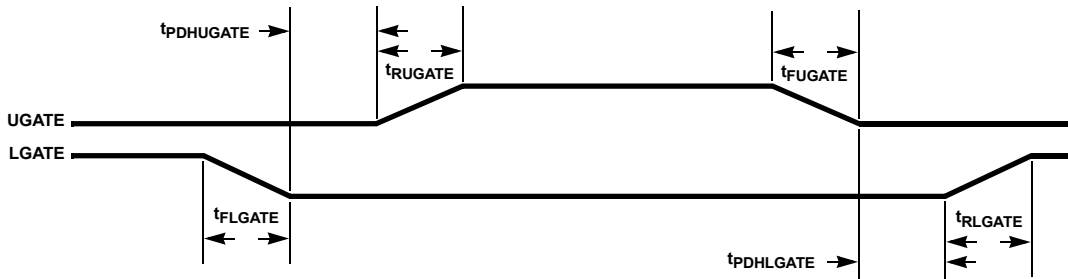
**Electrical Specifications** Boldface limits apply over the operating temperature range. (Continued)

PARAMETER	TEST CONDITIONS	MIN (Note 7)	TYP	MAX (Note 7)	UNITS
<b>POWER GOOD</b>					
Overvoltage Threshold	VSEN Rising	<b>VDAC + 220mV</b>		<b>VDAC + 325mV</b>	V
Undervoltage Threshold	VSEN Falling	<b>VDAC - 345mV</b>		<b>VDAC - 190mV</b>	mV
Power Good Hysteresis			50		mV
<b>OVERVOLTAGE PROTECTION</b>					
OVP Trip Level	V <sub>DAC</sub> = 1.1V	<b>1.75</b>	1.79	<b>1.85</b>	V
OVP Lower Gate Release Threshold		<b>0.35</b>			V
<b>SWITCHING TIME (Note 6) [See "Timing Diagram" on page 12]</b>					
UGATE Rise Time	t <sub>RUGATE</sub> ; V <sub>PVCC</sub> = 8V, 3nF Load, 10% to 90%		26		ns
LGATE Rise Time	t <sub>RLGATE</sub> ; V <sub>PVCC</sub> = 8V, 3nF Load, 10% to 90%		18		ns
UGATE Fall Time	t <sub>FUGATE</sub> ; V <sub>PVCC</sub> = 12V, 3nF Load, 90% to 10%		18		ns
LGATE Fall Time	t <sub>FLGATE</sub> ; V <sub>PVCC</sub> = 12V, 3nF Load, 90% to 10%		12		ns
UGATE Turn-On Non-overlap	t <sub>PDHUGATE</sub> ; V <sub>PVCC</sub> = 12V, 3nF Load, Adaptive		10		ns
LGATE Turn-On Non-overlap	t <sub>PDHLGATE</sub> ; V <sub>PVCC</sub> = 12V, 3nF Load, Adaptive		10		ns
<b>GATE DRIVE RESISTANCE (Note 6)</b>					
Upper Drive Source Resistance	V <sub>PVCC</sub> = 12V, 15mA Source Current		2.5		Ω
Upper Drive Sink Resistance	V <sub>PVCC</sub> = 12V, 15mA Sink Current		2.0		Ω
Lower Drive Source Resistance	V <sub>PVCC</sub> = 12V, 15mA Source Current		1.6		Ω
Lower Drive Sink Resistance	V <sub>PVCC</sub> = 12V, 15mA Sink Current		1.1		Ω
<b>SVI INTERFACE</b>					
SVC, SVD Input HIGH (VIH)	Percentage of V <sub>VDDIO</sub>	<b>70</b>			%
SVC, SVD Input LOW (VIL)	Percentage of V <sub>VDDIO</sub>			<b>30</b>	%
Schmitt Trigger Input Hysteresis	Percentage of V <sub>VDDIO</sub>	<b>15</b>	20	<b>25</b>	%
SVD Low Level Output Voltage	511Ω Resistor to 1.8V			<b>0.4</b>	V
SVC, SVD Leakage				<b>±5</b>	μA
<b>I<sup>2</sup>C INTERFACE</b>					
SCL, SDA Input HIGH (VIH)		<b>1.8</b>			V
SCL, SDA Input LOW (VIL)				<b>1.0</b>	V
Schmitt Trigger Input Hysteresis		<b>0.18</b>		<b>0.5</b>	V
SDA Low Level Output Voltage	1kΩ Resistor to 3.3V			<b>0.4</b>	V
SCL, SDA Leakage				<b>±5</b>	μA

## NOTES:

- Limits should be considered typical and are not production tested.
- Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by characterization and are not production tested.

# Timing Diagram



## Operation

The ISL6329 utilizes a multiphase architecture to provide a low cost, space saving power conversion solution for the processor core voltage. The controller also implements a simple single phase architecture to provide the Northbridge voltage on the same chip.

*NOTE: All references to VCC refer to the VCC pin or the node that is tied to the VCC pin. This should not be confused with the bias voltage as the bias rail can be separated from the VCC node by an RC filter resistor.*

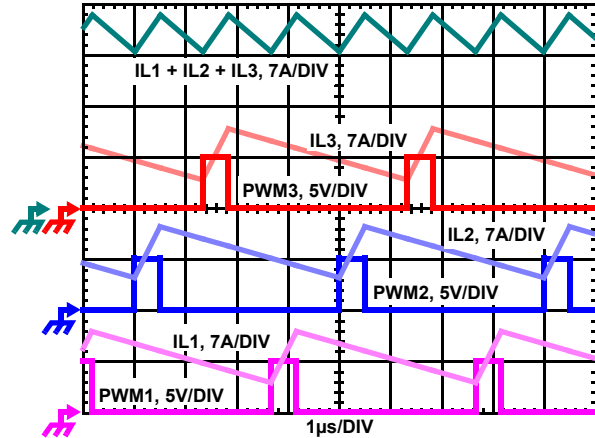
## Multiphase Power Conversion

Microprocessor load current profiles have changed to the point that the advantages of multiphase power conversion are impossible to ignore. The technical challenges associated with producing a single-phase converter that is both cost-effective and thermally viable have forced a change to the cost-saving approach of multiphase. The ISL6329 controller helps simplify implementation by integrating vital functions and requiring minimal external components. The “Controller Block Diagram” on page 3 provides a top level view of the multiphase power conversion using the ISL6329 controller.

## Interleaving

The switching of each channel in a multiphase converter is timed to be symmetrically out-of-phase with each of the other channels. In a 3-phase converter, each channel switches 1/3 cycle after the previous channel and 1/3 cycle before the following channel. As a result, the 3-phase converter has a combined ripple frequency three times greater than the ripple frequency of any one phase. In addition, the peak-to-peak amplitude of the combined inductor currents is reduced in proportion to the number of phases (Equations 2 and 3). Increased ripple frequency and lower ripple amplitude mean that the designer can use less per-channel inductance and lower total output capacitance for any performance specification.

Figure 1 illustrates the multiplicative effect on output ripple frequency. The three channel currents (IL1, IL2, and IL3) combine to form the AC ripple current and the DC load current. The ripple component has three times the ripple frequency of each individual channel current. Each PWM pulse is terminated 1/3 of a cycle after the PWM pulse of the previous phase. The peak-to-peak current for each phase is about 7A, and the DC components of the inductor currents combine to feed the load.



**FIGURE 1. PWM AND INDUCTOR-CURRENT WAVEFORMS FOR 3-PHASE CONVERTER**

To understand the reduction of ripple current amplitude in the multiphase circuit, examine Equation 2, which represents an individual channel peak-to-peak inductor current.

$$I_{PP} = \frac{(V_{IN} - V_{OUT})V_{OUT}}{L f_S V_{IN}} \tag{EQ. 2}$$

In Equation 2,  $V_{IN}$  and  $V_{OUT}$  are the input and output voltages respectively,  $L$  is the single-channel inductor value, and  $f_S$  is the switching frequency.

The output capacitors conduct the ripple component of the inductor current. In the case of multiphase converters, the capacitor current is the sum of the ripple currents from each of the individual channels. Compare Equation 2 to the expression for the peak-to-peak current after the summation of  $N$  symmetrically phase-shifted inductor currents in Equation 3. Peak-to-peak ripple current decreases by an amount proportional to the number of channels. Output-voltage ripple is a function of capacitance, capacitor equivalent series resistance (ESR), and inductor ripple current. Reducing the inductor ripple current allows the designer to use fewer or less costly output capacitors.

$$I_{C,PP} = \frac{(V_{IN} - N V_{OUT})V_{OUT}}{L f_S V_{IN}} \tag{EQ. 3}$$

Another benefit of interleaving is to reduce input ripple current. Input capacitance is determined in part by the maximum input ripple current. Multiphase topologies can improve overall system cost and size by lowering input ripple current and allowing the designer to reduce the cost of input capacitance. The example in

Figure 2 illustrates input currents from a 3-phase converter combining to reduce the total input ripple current.

The converter depicted in Figure 2 delivers 1.5V to a 36A load from a 12V input. The RMS input capacitor current is 5.9A. Compare this to a single-phase converter also stepping down 12V to 1.5V at 36A. The single-phase converter has 11.9A RMS input capacitor current. The single-phase converter must use an input capacitor bank with twice the RMS current capacity as the equivalent three-phase converter.

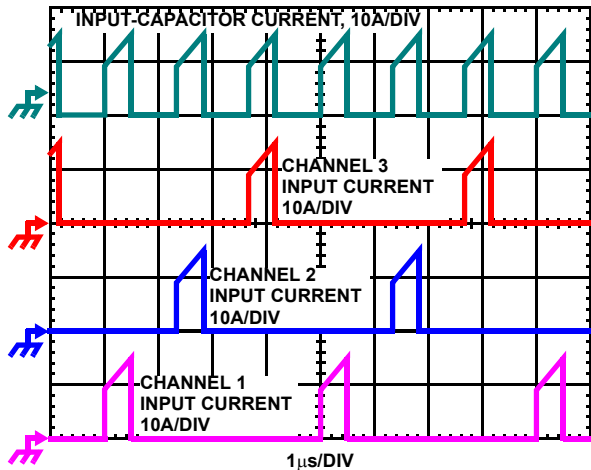


FIGURE 2. CHANNEL INPUT CURRENTS AND INPUT-CAPACITOR RMS CURRENT FOR 3-PHASE CONVERTER

Figures 26, 27 and 28 in the section entitled “Input Capacitor Selection” on page 33 can be used to determine the input-capacitor RMS current based on load current, duty cycle, and the number of channels. They are provided as aids in determining the optimal input capacitor solution.

## Active Pulse Positioning Modulated PWM Operation

The ISL6329 uses a proprietary Active Pulse Positioning (APP) modulation scheme to control the internal PWM signals that command each channel’s driver to turn their upper and lower MOSFETs on and off. The time interval in which a PWM signal can occur is generated by an internal clock, whose cycle time is the inverse of the switching frequency set by the resistor between the FS pin and ground. The advantage of Intersil’s proprietary Active Pulse Positioning (APP) modulator is that the PWM signal has the ability to turn on at any point during this PWM time interval, and turn off immediately after the PWM signal has transitioned high. This is important because it allows the controller to quickly respond to output voltage drops associated with current load spikes, while avoiding the ring back affects associated with other modulation schemes.

The PWM output state is driven by the position of the error amplifier output signal,  $V_{COMP}$ , minus the current correction signal relative to the proprietary modulator ramp waveform as illustrated in Figure 3. At the beginning of each PWM time interval, this modified  $V_{COMP}$  signal is compared to the internal modulator waveform. As long as the modified  $V_{COMP}$  voltage is lower than the modulator waveform voltage, the PWM signal is commanded low. The internal MOSFET driver detects the low

state of the PWM signal and turns off the upper MOSFET and turns on the lower synchronous MOSFET. When the modified  $V_{COMP}$  voltage crosses the modulator ramp, the PWM output transitions high, turning off the synchronous MOSFET and turning on the upper MOSFET. The PWM signal will remain high until the modified  $V_{COMP}$  voltage crosses the modulator ramp again. When this occurs the PWM signal will transition low again.

During each PWM time interval the PWM signal can only transition high once. Once PWM transitions high it can not transition high again until the beginning of the next PWM time interval. This prevents the occurrence of double PWM pulses occurring during a single period.

To further improve the transient response, ISL6329 also implements Intersil’s proprietary Adaptive Phase Alignment (APA) technique, which turns on all phases together under transient events with large step current. With both APP and APA control, ISL6329 can achieve excellent transient performance and reduce the demand on the output capacitors.

## Adaptive Phase Alignment (APA)

When a load is applied, the output will fall in direct relation to the amount of load being applied and the speed at which the load is being applied. The ISL6329 monitors the output differentially through the VSEN pin. If the sensed voltage drops quickly by a user programmable magnitude ( $V_{APATRIP}$ ), all of the upper MOSFETs will immediately be turned on simultaneously. The trip level is relative, not absolute, and can be programmed through a resistor and capacitor tied in parallel from the APA pin to ground.

$$R_{APA} = \frac{V_{APATRIP}}{1.75\mu A} \quad (EQ. 4)$$

A 3900pF, X7R capacitor is required to be placed in parallel to the APA resistor.

## PWM Operation

The timing of each core channel is set by the number of active channels. Channel detection on the ISEN2-, ISEN3-, ISEN4-, ISEN5- and ISEN6- pins selects 1-channel to 6-channel operation for the ISL6329. The switching cycle is defined as the time between PWM pulse termination signals of each channel. The cycle time of the pulse signal is the inverse of the switching frequency set by the resistor between the FS pin and ground (or VCC). The PWM signals command the MOSFET driver to turn on/off the channel MOSFETs.

The channel firing order for 6-channel operation is 1-2-3-4-5-6. For 5-channel operation, the order is 1-2-3-4-5. For 4-channel operation, the channel firing order is 1-2-3-4. For 3-channel operation, the channel firing order is 1-2-3.

Connecting ISEN6- to VCC selects five channel operation. To set four channel operation, both ISEN6- and ISEN5- must be tied to VCC. Similarly, to set three channel operation, ISEN6-, ISEN5- and ISEN4- must be tied to VCC. For two channel operation, ISEN6-, ISEN5-, ISEN4- and ISEN3- must be tied to VCC. To set single channel operation, ISEN6-, ISEN5- ISEN4- ISEN3- and ISEN2- must all be tied to VCC. Tying the negative current sense pin of a channel to VCC while the higher numbered channels are still active should not be done. For example, tying ISEN4- to VCC should not be done if ISEN5- and/or ISEN6- are not tied to VCC.

## Continuous Current Sampling

In order to realize proper current-balance, the currents in each channel are sampled continuously every switching cycle. During this time, the current-sense amplifier uses the ISEN inputs to reproduce a signal proportional to the inductor current,  $I_L$ . This sensed current,  $I_{SEN}$ , is simply a scaled version of the inductor current.

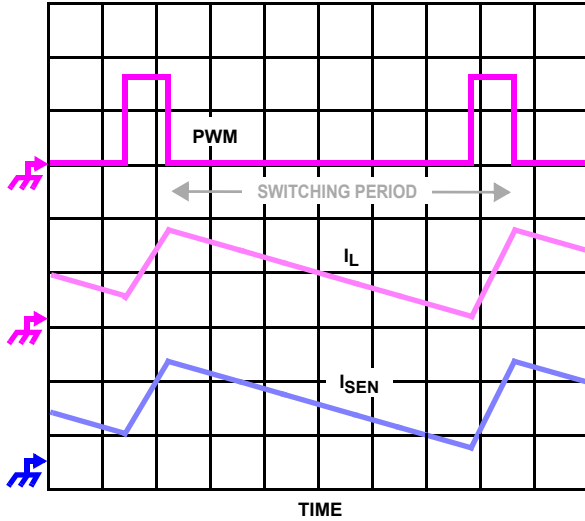


FIGURE 3. CONTINUOUS CURRENT SAMPLING

The ISL6329 supports Inductor DCR current sensing to continuously sample each channel's current for channel-current balance. The internal circuitry shown in Figure 4 represents Channel  $n$  of an  $n$ -Channel converter. This circuitry is repeated for each channel in the converter, but may not be active depending on how many channels are operating.

Inductor windings have a characteristic distributed resistance or DCR (Direct Current Resistance). For simplicity, the inductor DCR is considered as a separate lumped quantity, as shown in Figure 4. The channel current  $I_{L_n}$ , flowing through the inductor, passes through the DCR. Equation 5 shows the S-domain equivalent voltage,  $V_L$ , across the inductor.

$$V_L(s) = I_{L_n} \cdot (s \cdot L + \text{DCR}) \quad (\text{EQ. 5})$$

A simple R-C network across the inductor ( $R_1$ ,  $R_2$  and  $C$ ) extracts the DCR voltage, as shown in Figure 6. The voltage across the sense capacitor,  $V_C$ , can be shown to be proportional to the channel current  $I_{L_n}$ , shown in Equation 6.

$$V_C(s) = \frac{\left(\frac{s \cdot L}{\text{DCR}} + 1\right)}{\left(s \cdot \frac{(R_1 \cdot R_2)}{R_1 + R_2} \cdot C + 1\right)} \cdot K \cdot \text{DCR} \cdot I_{L_n} \quad (\text{EQ. 6})$$

Where:

$$K = \frac{R_2}{R_2 + R_1} \quad (\text{EQ. 7})$$

If the R-C network components are selected such that the RC time constant matches the inductor  $L/\text{DCR}$  time constant (see Equation 8), then  $V_C$  is equal to the voltage drop across the DCR

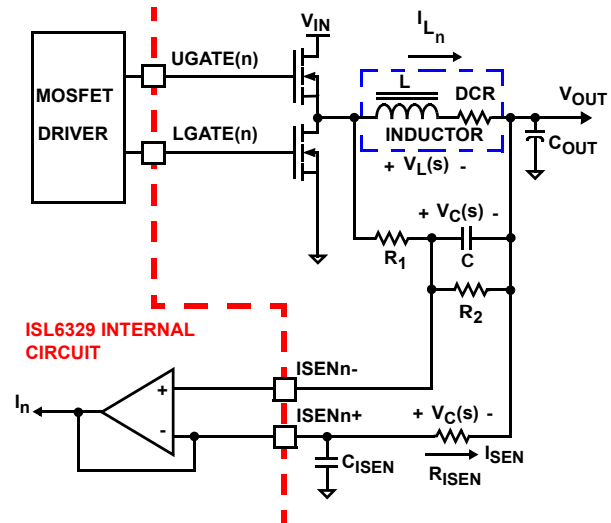


FIGURE 4. INDUCTOR DCR CURRENT SENSING CONFIGURATION

multiplied by the ratio of the resistor divider,  $K$ . If a resistor divider is not being used, the value for  $K$  is 1.

$$\frac{L}{\text{DCR}} = \frac{R_1 \cdot R_2}{R_1 + R_2} \cdot C \quad (\text{EQ. 8})$$

The capacitor voltage  $V_C$  is then replicated across the effective internal sense resistor,  $R_{ISEN}$ . This develops a current through  $R_{ISEN}$  which is proportional to the inductor current. This current,  $I_{SEN}$ , is continuously sensed and is then used by the controller for load-line regulation, channel-current balancing, and overcurrent detection and limiting. Equation 9 shows that the proportion between the channel current,  $I_L$ , and the sensed current,  $I_{SEN}$ , is driven by the value of the effective sense resistance,  $R_{ISEN}$ , and the DCR of the inductor.

$$I_{SEN} = I_L \cdot \frac{\text{DCR}}{R_{ISEN}} \quad (\text{EQ. 9})$$

The Northbridge regulator samples the load current in the same manner as the Core regulator does.

The sampled currents,  $I_n$ , from each active channel are summed together and divided by the number of active channels. The resulting cycle average current,  $I_{AVG}$ , provides a measure of the total load-current demand on the converter during each switching cycle. Assuming that the current in all the active channels is balanced, the average sensed current can be calculated from Equation 10.

$$I_{AVG} = \frac{I_{\text{Load}}}{N} \cdot \frac{\text{DCR}}{R_{ISEN}} \quad (\text{EQ. 10})$$

In the ISL6329, the average scaled version of the load current,  $I_{AVG}$ , has a  $100\mu\text{A}$  range. At  $100\mu\text{A}$ , the Overcurrent Protection circuitry is enabled (refer to the "Overvoltage Protection" on page 21 for detailed information). It is recommended that the maximum load current correlate to an average sensed current,  $I_{AVG}$ , of  $80\mu\text{A}$ .

A capacitor,  $C_{ISEN}$ , should be placed between the ISENn+ pin and ground. The value of the capacitor can be calculated using Equation 11.

$$C_{ISEN} = \frac{9.5\text{ns}}{R_{ISEN}} \quad (\text{EQ. 11})$$

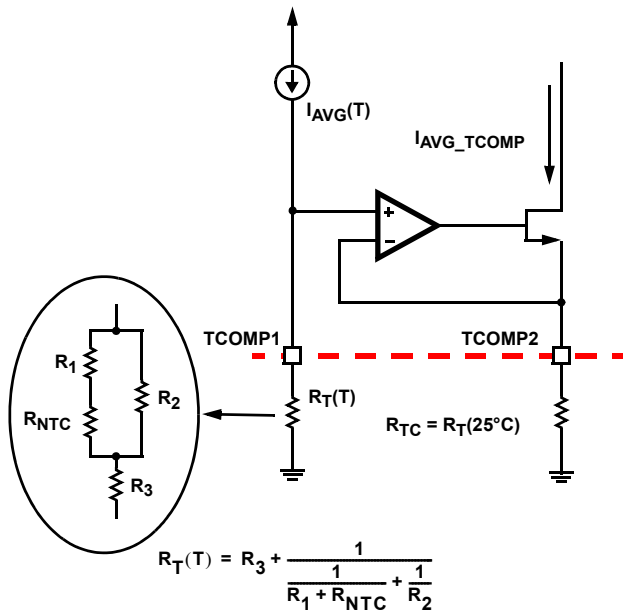


FIGURE 5. AVERAGE CURRENT TEMPERATURE COMPENSATION

### Temperature Compensated Current Sensing

As the load increases, the conduction losses in the output inductors will cause the temperature of the inductors to rise. As the inductor temperature rises, the DCR of the output inductors will also rise. An increase in the DCR will result in an increase in the sensed current even if the load current remains constant. To counteract this error in the sensed current, the ISL6329 features a temperature compensating circuit that utilizes an NTC resistor to adjust the average current as inductor temperature increases. Figure 5 shows the implementation of the ISL6329 average current temperature compensation. The temperature dependent resistor,  $R_T(T)$ , is a combination of resistors and an NTC which create an approximate linearization of the NTC resistor (refer to Equation 12). Resistors  $R_1$ ,  $R_2$  and  $R_3$  should be adjusted so that Equation 13 is satisfied.

$$R_T(T) = R_3 + \frac{1}{\frac{1}{R_1 + R_{NTC}} + \frac{1}{R_2}} \tag{EQ. 12}$$

$$R_T(T) = \frac{DCR(25^\circ C)}{DCR(T)} \cdot R_{TC} \tag{EQ. 13}$$

Where  $R_{TC} = R_T(25^\circ C)$

### LOAD MONITORING

The TCOMP2 pin can be utilized to monitor the load current. The voltage across the  $R_{TC}$  resistor is a temperature compensated representation of the load current. The load current is given by Equation 14.

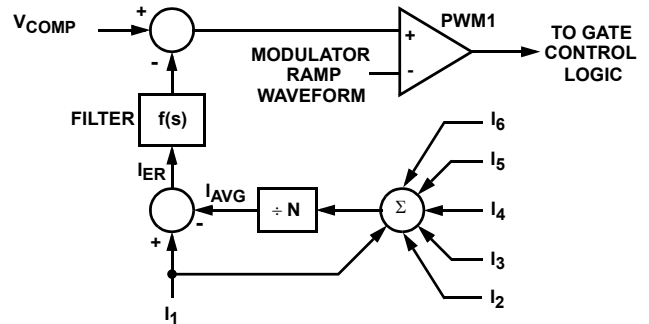
$$I_{LOAD} = 8 \cdot \frac{V_{TCOMP2}}{R_{TC}} \cdot \frac{R_{ISEN}}{DCR} \tag{EQ. 14}$$

Where  $R_{ISEN}$  is the current sense resistor value and DCR is the DC resistance of the output inductors. It is recommended that a high impedance buffer be used when monitoring the voltage on the TCOMP2 pin.

### Channel-Current Balance

One important benefit of multiphase operation is the thermal advantage gained by distributing the dissipated heat over multiple devices and greater area. By doing this the designer avoids the complexity of driving parallel MOSFETs and the expense of using expensive heat sinks and exotic magnetic materials.

In order to realize the thermal advantage, it is important that each channel in a multiphase converter be controlled to carry about the same amount of current at any load level. To achieve this, the currents through each channel must be sampled every switching cycle. The sampled currents,  $I_n$ , from each active channel are summed together and divided by the number of active channels. The resulting cycle average current,  $I_{AVG}$ , provides a measure of the total load-current demand on the converter during each switching cycle. Channel-current balance is achieved by comparing the sampled current of each channel to the cycle average current, and making the proper adjustment to each channel pulse width based on the error. Intersil's patented current-balance method is illustrated in Figure 6, with error correction for Channel 1 represented. In the figure, the cycle average current,  $I_{AVG}$ , is compared with the Channel 1 sample,  $I_1$ , to create an error signal  $I_{ER}$ .



NOTE: Channels 2, 3, 4, 5 and 6 are optional.

FIGURE 6. CHANNEL-1 PWM FUNCTION AND CURRENT-BALANCE ADJUSTMENT

The filtered error signal modifies the pulse width commanded by  $V_{COMP}$  to correct any unbalance and force  $I_{ER}$  toward zero. The same method for error signal correction is applied to each active channel.

### Serial VID Interface (SVI)

The on-board Serial VID interface (SVI) circuitry allows the processor to directly drive the core voltage and Northbridge voltage reference level within the ISL6329. The SVC and SVD states are decoded with direction from the PWROK input as described in the sections that follow. The ISL6329 uses a digital to analog converter (DAC) to generate a reference voltage based on the decoded SVI value. See Figure 7 for a simple SVI interface timing diagram.

### Pre-PWROK METAL VID

At start-up, the controller decodes the SVC and SVD inputs to determine the Pre-PWROK metal VID setting. Once the POR circuitry is satisfied, the ISL6329 begins decoding the inputs per Table 1. Once the EN input exceeds the rising enable threshold, the ISL6329 saves the Pre-PWROK metal VID value in an on-board holding register and passes this target to the internal DAC circuitry.

TABLE 1. PRE-PWROK METAL VID CODES

SVC	SVD	OUTPUT VOLTAGE (V)
0	0	1.1
0	1	1.0
1	0	0.9
1	1	0.8

The Pre-PWROK metal VID code is decoded and latched on the rising edge of the enable signal. Once enabled, the ISL6329 passes the Pre-PWROK metal VID code on to internal DAC circuitry. The internal DAC circuitry begins to ramp both the VDD and VDDNB planes to the decoded Pre-PWROK metal VID output level. The digital soft-start circuitry actually stair steps the internal reference to the target gradually over a fixed interval. The controlled ramp of both output voltage planes reduces in-rush current during the soft-start interval. At the end of the soft-start interval, the VDDPWRGD output transitions high indicating both output planes are within regulation limits.

### SVI Mode

Once the controller has successfully soft-started and VDDPWRGD transitions high, the Northbridge SVI interface can assert PWROK to signal the ISL6329 to prepare for SVI commands. The controller actively monitors the SVI interface for set VID commands to move the plane voltages to start-up VID values. Details of the SVI Bus protocol are provided in the AMD Design Guide for Voltage Regulator Controllers Accepting Serial VID Codes specification.

Once the set VID command is received, the ISL6329 decodes the information to determine which plane and the VID target required. See Table 2. The internal DAC circuitry steps the required output plane voltage to the new VID level. During this time one or both of the planes could be targeted. In the event the core voltage plane, VDD, is commanded to power off by serial VID commands, the VDDPWRGD signal remains asserted. The Northbridge voltage plane must remain active during this time.

If the PWROK input is de-asserted, then the controller steps both VDD and VDDNB planes back to the stored Pre-PWROK metal VID level in the holding register from initial soft-start. No attempt is made to read the SVC and SVD inputs during this time. If PWROK is reasserted, then the on-board SVI interface waits for a set VID command.

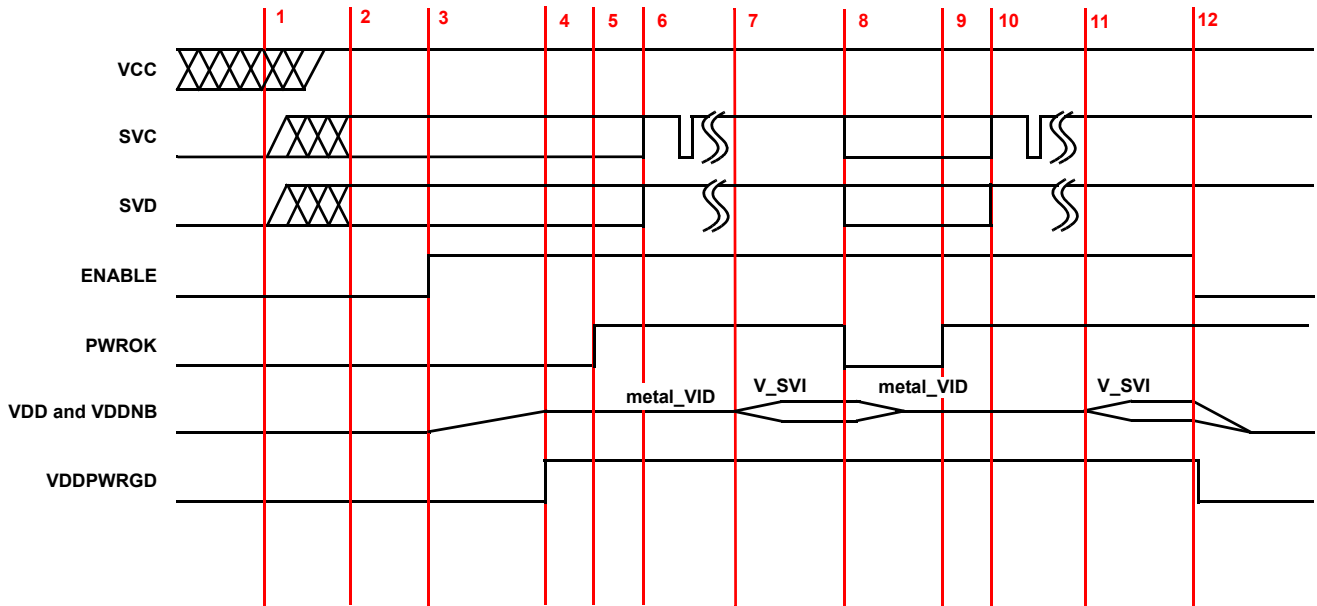


FIGURE 7. SVI INTERFACE TIMING DIAGRAM: TYPICAL PRE-PWROK METAL VID START-UP



TABLE 2. SERIAL VID CODES

SVID[6:0]	VOLTAGE (V)	SVID[6:0]	VOLTAGE (V)	SVID[6:0]	VOLTAGE (V)	SVID[6:0]	VOLTAGE (V)
000_0000b	1.5500	010_0000b	1.1500	100_0000b	0.7500	110_0000b	0.3500*
000_0001b	1.5375	010_0001b	1.1375	100_0001b	0.7375	110_0001b	0.3375*
000_0010b	1.5250	010_0010b	1.1250	100_0010b	0.7250	110_0010b	0.3250*
000_0011b	1.5125	010_0011b	1.1125	100_0011b	0.7125	110_0011b	0.3125*
000_0100b	1.5000	010_0100b	1.1000	100_0100b	0.7000	110_0100b	0.3000*
000_0101b	1.4875	010_0101b	1.0875	100_0101b	0.6875	110_0101b	0.2875*
000_0110b	1.4750	010_0110b	1.0750	100_0110b	0.6750	110_0110b	0.2750*
000_0111b	1.4625	010_0111b	1.0625	100_0111b	0.6625	110_0111b	0.2625*
000_1000b	1.4500	010_1000b	1.0500	100_1000b	0.6500	110_1000b	0.2500*
000_1001b	1.4375	010_1001b	1.0375	100_1001b	0.6375	110_1001b	0.2375*
000_1010b	1.4250	010_1010b	1.0250	100_1010b	0.6250	110_1010b	0.2250*
000_1011b	1.4125	010_1011b	1.0125	100_1011b	0.6125	110_1011b	0.2125*
000_1100b	1.4000	010_1100b	1.0000	100_1100b	0.6000	110_1100b	0.2000*
000_1101b	1.3875	010_1101b	0.9875	100_1101b	0.5875	110_1101b	0.1875*
000_1110b	1.3750	010_1110b	0.9750	100_1110b	0.5750	110_1110b	0.1750*
000_1111b	1.3625	010_1111b	0.9625	100_1111b	0.5625	110_1111b	0.1625*
001_0000b	1.3500	011_0000b	0.9500	101_0000b	0.5500	111_0000b	0.1500*
001_0001b	1.3375	011_0001b	0.9375	101_0001b	0.5375	111_0001b	0.1375*
001_0010b	1.3250	011_0010b	0.9250	101_0010b	0.5250	111_0010b	0.1250*
001_0011b	1.3125	011_0011b	0.9125	101_0011b	0.5125	111_0011b	0.1125*
001_0100b	1.3000	011_0100b	0.9000	101_0100b	0.5000	111_0100b	0.1000*
001_0101b	1.2875	011_0101b	0.8875	101_0101b	0.4875*	111_0101b	0.0875*
001_0110b	1.2750	011_0110b	0.8750	101_0110b	0.4750*	111_0110b	0.0750*
001_0111b	1.2625	011_0111b	0.8625	101_0111b	0.4625*	111_0111b	0.0625*
001_1000b	1.2500	011_1000b	0.8500	101_1000b	0.4500*	111_1000b	0.0500*
001_1001b	1.2375	011_1001b	0.8375	101_1001b	0.4375*	111_1001b	0.0375*
001_1010b	1.2250	011_1010b	0.8250	101_1010b	0.4250*	111_1010b	0.0250*
001_1011b	1.2125	011_1011b	0.8125	101_1011b	0.4125*	111_1011b	0.0125*
001_1100b	1.2000	011_1100b	0.8000	101_1100b	0.4000*	111_1100b	OFF
001_1101b	1.1875	011_1101b	0.7875	101_1101b	0.3875*	111_1101b	OFF
001_1110b	1.1750	011_1110b	0.7750	101_1110b	0.3750*	111_1110b	OFF
001_1111b	1.1625	011_1111b	0.7625	101_1111b	0.3625*	111_1111b	OFF

NOTE: \* Indicates a VID not required for AMD Family 10h processors.

## Power Savings Mode: PSI\_L

Bit 7 of the Serial VID codes transmitted as part of the 8-bit data stream over the SVI bus is allocated for the PSI\_L. If bit 7 is 0, then the processor is at an optimal load for the regulator to enter power savings mode. If bit 7 is 1, then the regulator should not be in power savings mode.

With the ISL6329, Power Savings mode is realized through phase shedding, Gate Voltage Optimization and Diode Emulation. Once a Serial VID command with Bit 7 set to 0 is received, the ISL6329 will shed phases in a sequential manner until then minimum phase count for PSI is reached. The minimum phase count for PSI can be programmed via the FS pin to be either 1 phase or 2 phases. If the FS resistor is tied to ground, then the minimum phase count in PSI is 1 phase. If the

FS resistor is tied to VCC then the minimum phase count in PSI is 2 phases. Channels are shed in reverse sequential order so that the highest numbered channel that is active will be shed first. When a phase is shed, that phase will not go into a tri-state mode until that phase would have had its PWM go HIGH.

When leaving Power Savings Mode, through the reception of a Serial VID command with Bit 7 set to 1, the ISL6329 will sequentially turn on phases starting with lowest numbered inactive channel. When a phase is being reactivated, it will not leave a tri-state until the PWM of that phase goes HIGH.

If, while in Power Savings Mode, a Serial VID command is received that forces a VID level change while maintaining Bit 7 at 0, the ISL6329 will first exit the Power Savings Mode state as described previously. The output voltage will then be stepped up

or down to the appropriate VID level. Finally, the ISL6329 will then re-enter Power Savings Mode.

While in Power Savings Mode, the ISL6329 implements two features that effectively enhance the efficiency of the regulator even more. These features are Diode Emulation and Gate Voltage Optimization.

### DIODE EMULATION

While in Power Savings Mode, the active phases will behave as if they are in a standard buck configuration. To accomplish this, the lower MOSFET is turned on only while there is current flowing to the load. This behavior emulates the diode in a standard buck. The conduction loss across the  $R_{DS(on)}$  of the MOSFET, however, is much less than a diode, resulting in a measurable power savings.

### GATE VOLTAGE OPTIMIZATION

While in Power Savings Mode, the gate drive voltage for the lower MOSFETs of the active phases is reduced from the nominal 12V that is utilized in Normal mode to 5.75V. Lowering the gate drive voltage can have an appreciable effect on the efficiency of the converter.

In order to utilize 5V gate drive at all times, 5V should be tied to the PVCC pin and the GVOT pin should be shorted to the PVCC pin. This configuration will allow for 5V gate drive in all modes of operation.

### Voltage Regulation

The integrating compensation network shown in Figure 8 insures that the steady-state error in the output voltage is limited only to the error in the reference voltage and offset errors in the OFS current source, remote-sense and error amplifiers. Intersil specifies the guaranteed tolerance of the ISL6329 to include the combined tolerances of each of these elements.

The output of the error amplifier,  $V_{COMP}$ , is used by the modulator to generate the PWM signals. The PWM signals control the timing of the Internal MOSFET drivers and regulate the converter output so that the voltage at FB is equal to the voltage at REF. This will regulate the output voltage to be equal to Equation 15. The internal and external circuitry that controls voltage regulation is illustrated in Figure 8.

$$V_{OUT} = V_{REF} - V_{OFS} - V_{DROOP} \quad (\text{EQ. 15})$$

The ISL6329 incorporates differential remote-sense amplification in the feedback path. The differential sensing removes the voltage error encountered when measuring the output voltage relative to the controller ground reference point resulting in a more accurate means of sensing output voltage.

### Load-Line (Droop) Regulation

By adding a well controlled output impedance, the output voltage can effectively be level shifted in a direction which works to achieve a cost-effective solution can help to reduce the output-voltage spike that results from fast load-current demand changes.

The magnitude of the spike is dictated by the ESR and ESL of the output capacitors selected. By positioning the no-load voltage level near the upper specification limit, a larger negative spike can be sustained without crossing the lower limit. By adding a well controlled output

impedance, the output voltage under load can effectively be level shifted down so that a larger positive spike can be sustained without crossing the upper specification limit.

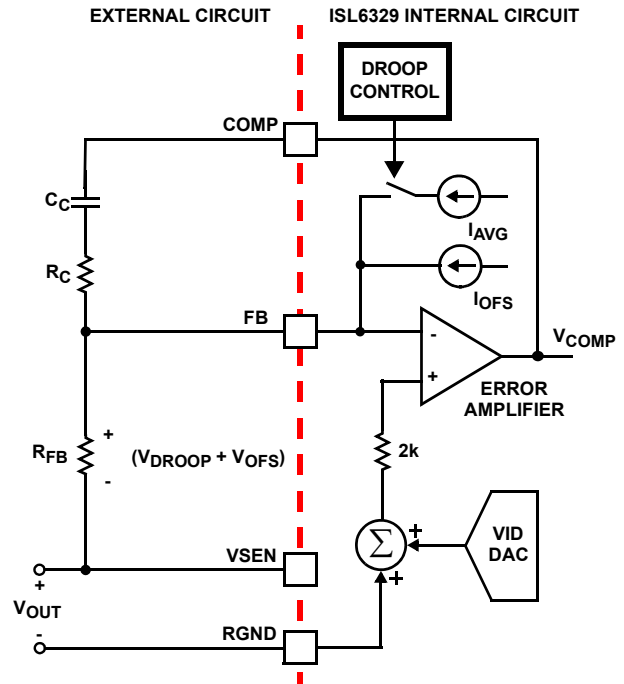


FIGURE 8. OUTPUT VOLTAGE AND LOAD-LINE REGULATION WITH OFFSET ADJUSTMENT

As shown in Figure 8, with the FS resistor tied to ground, the average current of all active channels,  $I_{AVG}$ , flows from FB through a load-line regulation resistor  $R_{FB}$ . The resulting voltage drop across  $R_{FB}$  is proportional to the output current, effectively creating an output voltage droop with a steady-state value defined as:

$$V_{DROOP} = I_{AVG} \cdot R_{FB} \quad (\text{EQ. 16})$$

The regulated output voltage is reduced by the droop voltage  $V_{DROOP}$ . The output voltage as a function of load current is shown in Equation 17.

$$V_{OUT} = V_{REF} - V_{OFS} - \left( \frac{I_{OUT}}{N} \cdot \frac{DCR}{R_{ISEN}} \cdot K \cdot R_{FB} \right) \quad (\text{EQ. 17})$$

In Equation 17,  $V_{REF}$  is the reference voltage,  $V_{OFS}$  is the programmed offset voltage,  $I_{OUT}$  is the total output current of the converter,  $K$  is the DC gain of the RC filter across the inductor ( $K$  is defined in Equation 8),  $N$  is the number of active channels, and  $DCR$  is the distributed inductor impedance value.

### Droop Control

The DRPCTRL (Droop Control) pin is used to enable and/or disable load line regulation on both the Core and Northbridge regulators. A single resistor tied from the DRPCTRL pin to Ground will program the ISL6329 to either enable or disable droop on both Core and Northbridge simultaneously.

TABLE 3. DRPCTRL FUNCTIONALITY

RESISTOR VALUE	CORE DROOP	NB DROOP
100kΩ	Disabled	Disabled
50kΩ	Disabled	Enabled
20kΩ	Enabled	Enabled
0Ω	Enabled	Disabled

**Output-Voltage Offset Programming**

The ISL6329 allows the designer to accurately adjust the offset voltage by connecting a resistor,  $R_{OFS}$ , from the OFS pin to VCC or GND. When  $R_{OFS}$  is connected between OFS and VCC, the voltage across it is regulated to 1.6V. This causes a proportional current ( $I_{OFS}$ ) to flow into the FB pin and out of the OFS pin. If  $R_{OFS}$  is connected to ground, the voltage across it is regulated to 0.3V, and  $I_{OFS}$  flows into the OFS pin and out of the FB pin. The offset current flowing through the resistor between VDIFF and FB will generate the desired offset voltage which is equal to the product ( $I_{OFS} \times R_{FB}$ ). These functions are shown in Figures 9 and 10.

Once the desired output offset voltage has been determined, use the following formulas to set  $R_{OFS}$ :

For Positive Offset (connect  $R_{OFS}$  to GND):

$$R_{OFS} = \frac{0.3 \times R_{FB}}{V_{OFFSET}} \quad (EQ. 18)$$

For Negative Offset (connect  $R_{OFS}$  to VCC):

$$R_{OFS} = \frac{1.6 \times R_{FB}}{V_{OFFSET}} \quad (EQ. 19)$$

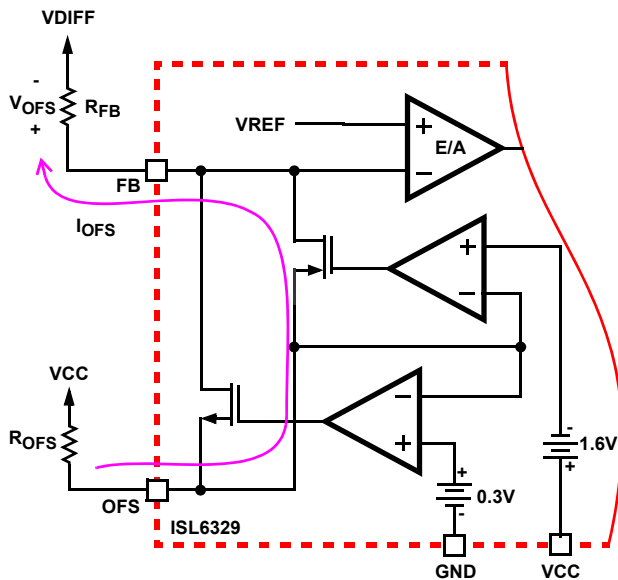


FIGURE 9. NEGATIVE OFFSET OUTPUT VOLTAGE PROGRAMMING

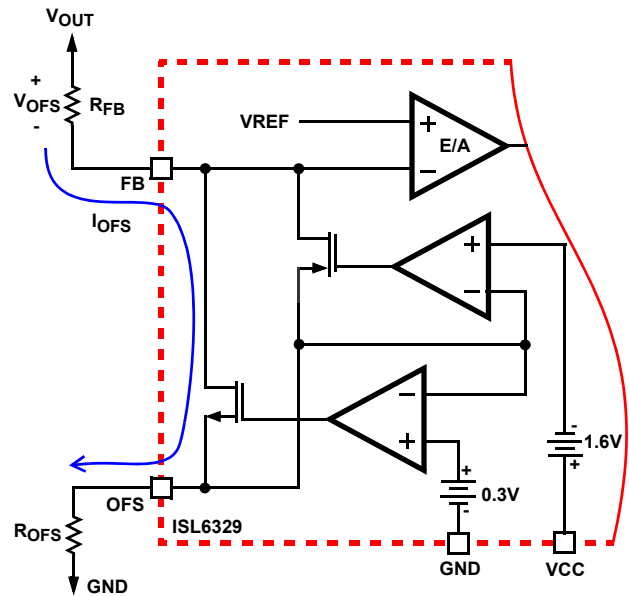


FIGURE 10. POSITIVE OFFSET OUTPUT VOLTAGE PROGRAMMING

**Dynamic VID**

The AMD processor does not step the output voltage commands up or down to the target voltage, but instead passes only the target voltage to the ISL6329 through the SVI interface. The ISL6329 manages the resulting VID-on-the-Fly transition in a controlled manner, supervising a safe output voltage transition without discontinuity or disruption. The ISL6329 slews the DAC at 2.8mV/μs until the DAC and target voltage are equal. Thus, the total time required for a dynamic VID transition is dependent only on the size of the DAC change. The slew rate can be adjusted through the I<sup>2</sup>C interface (see “I<sup>2</sup>C Bus Interface” on page 23).

**Advanced Adaptive Zero Shoot-Through Deadtime Control (Patent Pending)**

The integrated drivers incorporate a unique adaptive deadtime control technique to minimize deadtime, resulting in high efficiency from the reduced freewheeling time of the lower MOSFET body-diode conduction, and to prevent the upper and lower MOSFETs from conducting simultaneously. This is accomplished by ensuring either rising gate turns on its MOSFET with minimum and sufficient delay after the other has turned off.

During turn-off of the lower MOSFET, the PHASE voltage is monitored until it reaches a -0.3V/+0.8V (forward/reverse inductor current). At this time the UGATE is released to rise. An auto-zero comparator is used to correct the  $r_{DS(ON)}$  drop in the phase voltage preventing false detection of the -0.3V phase level during  $r_{DS(ON)}$  conduction period. In the case of zero current, the UGATE is released after 35ns delay of the LGATE dropping below 0.5V. When LGATE first begins to transition low, this quick transition can disturb the PHASE node and cause a false trip, so there is 20ns of blanking time once LGATE falls until PHASE is monitored.

Once the PHASE is high, the advanced adaptive shoot-through circuitry monitors the PHASE and UGATE voltages during a PWM falling edge and the subsequent UGATE turn-off. If either the UGATE falls to less than 1.75V above the PHASE or the PHASE falls to less than +0.8V, the LGATE is released to turn-on.

## Initialization

Prior to initialization, proper conditions must exist on the EN, VCC, PVCC, ISEN2-, ISEN3-, ISEN4-, ISEN5-, and ISEN6- pins. When the conditions are met, the controller begins soft-start. Once the output voltage is within the proper window of operation, the controller asserts VDDPWRGD.

### Power-On Reset

The ISL6329 requires VCC, PVCC and GVOT inputs to exceed their rising POR thresholds before the ISL6329 has sufficient bias to guarantee proper operation.

The bias voltage applied to VCC must reach the internal power-on reset (POR) rising threshold. Once this threshold is reached, the ISL6329 has enough bias to begin checking the driver POR inputs, EN, and channel detect portions of the initialization cycle. Hysteresis between the rising and falling thresholds assure the ISL6329 will not advertently turn off unless the bias voltage drops substantially (see “Electrical Specifications” on page 9).

The bias voltage applied to the PVCC pin powers the internal MOSFET drivers of each output channel. In order for the ISL6329 to begin operation, the PVCC input must exceed its POR rising threshold to guarantee proper operation of the internal drivers. Hysteresis between the rising and falling thresholds assure that once enabled, the ISL6329 will not inadvertently turn off unless the PVCC bias voltage drops substantially (see “Electrical Specifications” on page 9). Depending on the number of active CORE channels determined by the Phase Detect block, the external driver POR checking is supported by the Enable Comparator.

### Enable Comparator

The ISL6329 features a dual function enable input (EN) for enabling the controller and power sequencing between the controller and external drivers or another voltage rail. The enable comparator holds the ISL6329 in shutdown until the voltage at EN rises above 0.86V. The enable comparator has about 110mV of hysteresis to prevent bounce. It is important that the driver ICs reach their rising POR level before the ISL6329 becomes enabled. The schematic in Figure 12 demonstrates sequencing the ISL6329 with the ISL66XX family of Intersil MOSFET drivers, which require 12V bias.

When selecting the value of the resistor divider the driver maximum rising POR threshold should be used for calculating the proper resistor values. This will prevent improper sequencing events from creating false trips during soft-start.

If the controller is configured for 1- or 2-phase CORE operation, then the resistor divider can be used for sequencing the controller with another voltage rail. The resistor divider to EN should be selected using a similar approach as the previous driver discussion.

### Phase Detection

The ISEN2-, ISEN3-, ISEN4-, ISEN5-, and ISEN6- pins are monitored prior to soft-start to determine the number of active CORE channel phases.

If ISEN6- is tied to VCC, the controller will configure the channel firing order and timing for 5-phase operation. If ISEN6- and ISEN5- are tied to VCC, the controller will set the channel firing order and timing for 4-phase operation. If ISEN6-, ISEN5- and ISEN4- are tied to VCC, the controller will set the channel firing order and timing for 3-phase operation. If ISEN6-, ISEN5-, ISEN4- and ISEN3- are tied to VCC, the controller will set the channel firing order and timing for a 2-phase operation. The controller will configure itself as a single phase regulator if ISEN6-, ISEN5-, ISEN4-, ISEN3- and ISEN2- are tied to VCC (see “PWM Operation” on page 13 for details).

### Soft-Start Output Voltage Targets

Once the POR and Phase Detect blocks and enable comparator are satisfied, the controller will begin the soft-start sequence and will ramp the CORE and NB output voltages up to the SVI interface designated target level. Prior to soft-starting both CORE and NB outputs, the ISL6329 must check the state of the SVI interface inputs to determine the correct target voltages for both outputs. When the controller is enabled, the state of the SVD and SVC inputs are checked and the target output voltages set for both CORE and NB outputs are set by the DAC (see “Serial VID Interface (SVI)” on page 15). These targets will only change if the EN signal is pulled low or after a POR reset of VCC.

### Soft-Start

The soft-start sequence is composed of three periods, as shown in Figure 11. At the beginning of soft-start, the DAC immediately obtains the output voltage target. A 100µs fixed delay time, TDA, proceeds the output voltage rise. After this delay period the ISL6329 will begin ramping both CORE and NB output voltages to the programmed DAC level. The amount of time required to ramp the output voltage to the final DAC voltage is referred to as TDB, and can be calculated as shown in Equation 20.

$$TDB = \frac{V_{DAC}}{SR_{SS}} \quad (\text{EQ. 20})$$

Where the Soft-Start Slew Rate ( $SR_{SS}$ ) defaults to 2.8mV/µsec (typical). This slew rate, however, is programmable through the I<sup>2</sup>C interface.

After the DAC voltage reaches the final VID setting, PGOOD will be set to high.

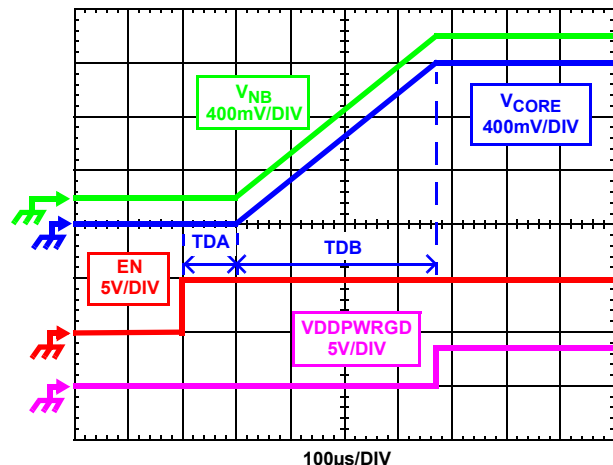


FIGURE 11. SOFT-START WAVEFORMS

### Pre-Biased Soft-Start

The ISL6329 also has the ability to start-up into a pre-charged output, without causing any unnecessary disturbance. The FB pin is monitored during soft-start, and should it be higher than the equivalent internal ramping reference voltage, the output drives hold both MOSFETs off.

Once the internal ramping reference exceeds the FB pin potential, the output drives are enabled, allowing the output to ramp from the pre-charged level to the final level dictated by the DAC setting. Should the output be pre-charged to a level exceeding the DAC setting, the output drives are enabled at the end of the soft-start period, leading to an abrupt correction in the output voltage down to the DAC-set level.

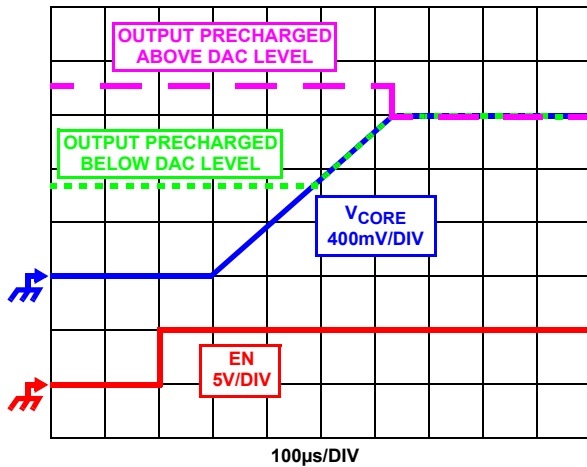


FIGURE 12. SOFT-START WAVEFORMS FOR ISL6329-BASED MULTIPHASE CONVERTER

Both CORE and NB output support start up into a pre-charged output.

### Fault Monitoring and Protection

The ISL6329 actively monitors both CORE and NB output voltages and currents to detect fault conditions. Fault monitors trigger protective measures to prevent damage to either load. One common power good indicator is provided for linking to external system monitors. The schematic in Figure 13 outlines the interaction between the fault monitors and the power good signal.

#### Power Good Signal

The power good pin (VDDPWRGD) is an open-drain logic output that signals whether or not the ISL6329 is regulating both NB and CORE output voltages within the proper levels, and whether any fault conditions exist. This pin should be tied to a +5V source through a resistor.

During shutdown and soft-start, VDDPWRGD pulls low and releases high after a successful soft-start and both output voltages are operating between the undervoltage and overvoltage limits. PGOOD transitions low when an undervoltage, overvoltage, or overcurrent condition is detected on either output or when the controller is disabled by a POR reset or EN. In the event of an overvoltage or overcurrent condition, the controller latches off and PGOOD will not return high. Pending a POR reset of the ISL6329 and successful soft-start, the PGOOD will return high.

### Overvoltage Protection

The ISL6329 constantly monitors the sensed output voltage on the VSEN pin to detect if an overvoltage event occurs. When the output voltage rises above the OVP trip level and exceeds the PGOOD OV limit actions are taken by the ISL6329 to protect the microprocessor load.

At the inception of an overvoltage event, both on-board lower gate pins are commanded low as are the active PWM outputs to the external drivers, the PGOOD signal is driven low, and the ISL6329 latches off normal PWM action. This turns on the all of the lower MOSFETs and pulls the output voltage below a level that might cause damage to the load. The lower MOSFETs remain driven ON until VDIFF falls below 400mV. The ISL6329 will continue to protect the load in this fashion as long as the overvoltage condition recurs. Once an overvoltage condition ends the ISL6329 latches off, and must be reset by toggling POR, before a soft-start can be re-initiated.

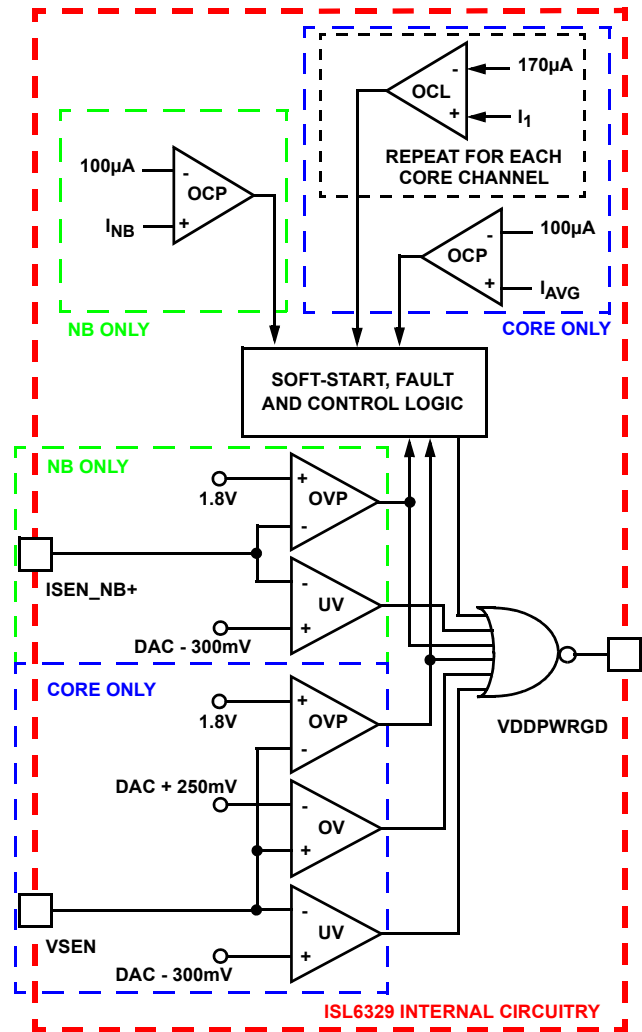


FIGURE 13. POWER GOOD AND PROTECTION CIRCUITRY

### Pre-POR Overvoltage Protection

Prior to PVCC, VCC and GVOT exceeding their POR levels, the ISL6329 is designed to protect either load from any overvoltage events that may occur. This is accomplished by means of an internal 10kΩ resistor tied from PHASE to LGATE, which turns on

the lower MOSFET to control the output voltage until the overvoltage event ceases or the input power supply cuts off. For complete protection, the low side MOSFET should have a gate threshold well below the maximum voltage rating of the load/microprocessor.

In the event that during normal operation if the PVCC, VCC or GVOT voltage falls back below the POR threshold, the pre-POR overvoltage protection circuitry reactivates to protect from any more pre-POR overvoltage events.

## Undervoltage Detection

The undervoltage threshold is set at VDAC - 300mV typical. When the output voltage (VSEN-RGND) is below the undervoltage threshold, PGOOD gets pulled low. No other action is taken by the controller. PGOOD will return high if the output voltage rises above VDAC - 250mV typical.

## Overcurrent Protection

The ISL6329 takes advantage of the proportionality between the load current and the average current,  $I_{AVG}$ , to detect an overcurrent condition. See “Continuous Current Sampling” on page 14 and “Channel-Current Balance” on page 15 for more detail on how the average current is measured. Once the average current exceeds  $100\mu\text{A}$ , a comparator triggers the converter to begin overcurrent protection procedures.

The overcurrent trip threshold is dictated by the DCR of the inductors, the number of active channels, the DC gain of the inductor RC filter and the  $R_{ISEN}$  resistor. The overcurrent trip threshold is shown in Equation 21.

$$I_{OCP} = 100\mu\text{A} \cdot \frac{N}{K} \cdot \frac{R_{ISEN}}{DCR} \cdot \left( \frac{V_{IN} - N \cdot P \cdot V_{OUT}}{2 \cdot P \cdot L \cdot P \cdot f_S} \cdot \frac{V_{OUT}}{V_{IN}} \right) \quad (\text{EQ. 21})$$

Where:

$$K = \frac{R_2}{R_1 + R_2} \quad \text{See “Continuous Current Sampling” on page 14.}$$

$f_S$  = Switching Frequency

Equation 21 is valid for both the Core regulator and the Northbridge regulator. This equation includes the DC load current as well as the total ripple current contributed by all the phases. For the Northbridge regulator, N is 1.

During soft-start, the overcurrent trip point is boosted by a factor of 1.4. Instead of comparing the average measured current to  $100\mu\text{A}$ , the average current is compared to  $140\mu\text{A}$ . Immediately after soft-start is over, the comparison level changes to  $100\mu\text{A}$ . This is done to allow for start-up into an active load while still supplying output capacitor in-rush current.

## OVERCURRENT PROTECTION SHUTDOWN

At the beginning of overcurrent shutdown, the controller sets all of the UGATE and LGATE signals low, puts PWM3, PWM4, PWM5, and PWM6 (if active) in a high-impedance state, and forces VDDPWRGD low. This turns off all of the upper and lower MOSFETs. The system remains in this state for fixed period of 12ms. If the controller is still enabled at the end of this wait period, it will attempt a soft-start, as shown in Figure 14. If the fault remains, the trip-retry cycles will continue until either the

fault is cleared or for a total of seven attempts. If the fault is not cleared on the final attempt, the controller disables UGATE and LGATE signals for both Core and Northbridge and latches off requiring a POR of VCC to reset the ISL6329.

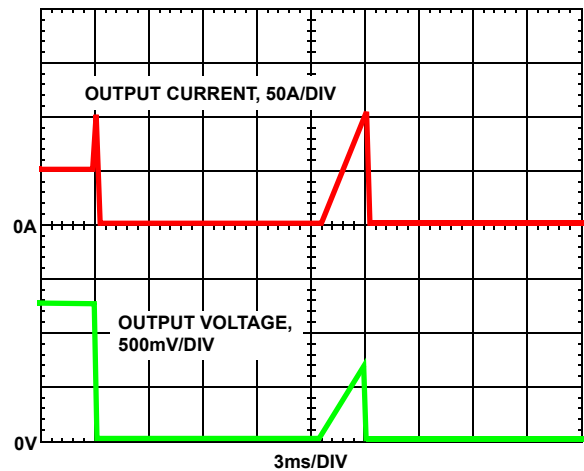


FIGURE 14. OVERCURRENT BEHAVIOR IN HICCUP MODE

It is important to note that during soft-start, the overcurrent trip point is increased by a factor of 1.4. If the fault draws enough current to trip overcurrent during normal run mode, it may not draw enough current during the soft-start ramp period to trip overcurrent while the output is ramping up. If a fault of this type is affecting the output, then the regulator will complete soft-start and the trip-retry counter will be reset to zero. Once the regulator has completed soft-start, the overcurrent trip point will return to its nominal setting and an overcurrent shutdown will be initiated. This will result in a continuous hiccup mode.

Note that the energy delivered during trip-retry cycling is much less than during full-load operation, so there is no thermal hazard.

## CORE REGULATOR OVERCURRENT

The ISL6329 features a Dual Overcurrent Protection (OCP) feature on the Core that allows AMD processors to “throttle” the load current beyond the normal OCP threshold for brief periods of time. These current spikes occur when idle processor cores are enabled. Dual OCP is not enabled until soft-start is complete.

When the Core average sensed current,  $I_{AVG}$ , exceeds  $100\mu\text{A}$ , the Core regulator does not immediately initiate overcurrent protection shutdown. The ISL6329 will, instead, source an amount of current out of the OCP pin that is equivalent to the amount of sensed current that exceeds  $100\mu\text{A}$ . A capacitor tied between the OCP pin and ground will immediately begin charging. If the voltage across the capacitor, and thus the voltage on the OCP pin, exceeds 2V then the ISL6329 will immediately initiate overcurrent protection shutdown. If  $I_{AVG}$  decreases to a level below  $100\mu\text{A}$  prior to the voltage on the OCP pin exceeding 2V, then the OCP pin is internally pulled to ground and the voltage on the OCP capacitor is discharged. If, at any time, the average sensed current exceeds  $145\mu\text{A}$ , the ISL6329 will immediately initiate overcurrent protection shutdown.

It is recommended that the maximum current spike correspond to an average sensed current level of  $120\mu\text{A}$ . It is also

recommended that if the maximum current spike load was applied to the Core regulator that overcurrent protection shutdown initiate after 1ms. This would require a 0.01 $\mu$ F capacitor be tied to the OCP pin. To calculate the OCP capacitor, use Equation 22.

$$C_{\text{OCP}} = \frac{20\mu\text{A} \cdot t_{\text{DELAY}}}{2V} \quad (\text{EQ. 22})$$

### NORTHBRIDGE REGULATOR OVERCURRENT

The Northbridge regulator does not incorporate dual OCP. When the sensed current of the Northbridge exceeds 100 $\mu$ A, Overcurrent Protection Shutdown is initiated. The overcurrent shutdown for the Northbridge regulator will only disable the MOSFET drivers for the Northbridge. Once 7 retry attempts have been executed unsuccessfully, the controller will disable UGATE and LGATE signals for both Core and Northbridge and will latch off requiring a POR of VCC to reset the ISL6329.

### OVERCURRENT PROTECTION IN POWER SAVINGS MODE

While in Power Savings Mode, the OCP trip point will be lower than when running in Normal Mode and there is no accommodation for current throttling. Equation 21 (with N = 1 for single phase PSI operation and with N = 2 for two phase PSI operation) will yield the OCP trip point for the Core regulator while in Power Savings mode.

If an overcurrent event should occur while the system is in Power Savings Mode, the ISL6329 will restart in the Normal state with the PSI\_L bit set to 1.

### Individual Channel Overcurrent Limiting

The ISL6329 has the ability to limit the current in each individual channel of the Core regulator without shutting down the entire regulator. This is accomplished by continuously comparing the sensed currents of each channel with a constant 170 $\mu$ A OCL reference current. If a channel's individual sensed current exceeds this OCL limit, the UGATE signal of that channel is immediately forced low, and the LGATE signal is forced high. This turns off the upper MOSFET(s), turns on the lower MOSFET(s), and stops the rise of current in that channel, forcing the current in the channel to decrease. That channel's UGATE signal will not be able to return high until the sensed channel current falls back below the 170 $\mu$ A reference.

## I<sup>2</sup>C Bus Interface

The ISL6329 includes an I<sup>2</sup>C bus interface which allows for user programmability of numerous operating parameters and programmability of the Power Savings Mode feature. Some of the parameters that can be adjusted through the I<sup>2</sup>C are:

1. **Voltage Margining Offset:** The DAC voltage can be offset in 25mV increments.
2. **VDDPWRGD Trip Level:** The PGOOD trip level for either the Core regulator or the Northbridge regulator can be increased.
3. **Overvoltage Trip Level:** The OVP trip level of either the Core or Northbridge regulator can be increased.
4. **Core Droop Gain:** The droop current can be decreased or halted.

### 5. Power Savings Mode Options:

- a. The number of phases to drop to in Power Savings Mode can be programmed
- b. The number of PWM cycles between dropping phases while entering Power Savings Mode can be programmed.
- c. The number of PWM cycles between adding phases when exiting Power Savings Mode can be programmed.
- d. Core Voltage Margining Offset can be Enabled or Disabled while in Power Savings Mode.
- e. The GVOT voltage level can be programmed

To adjust these parameters, data transmission to and from the ISL6329 must take place through the two wire I<sup>2</sup>C bus interface. The two wires of the I<sup>2</sup>C bus consist of the SDA line, over which all data is sent, and the SCL line, which is a clock signal used to synchronize sending/receiving of the data.

Both SDA and SCL are bidirectional lines, externally connected to a positive supply voltage via a pull-up resistor. Pull-up resistor values should be chosen to limit the input current to less than 3mA. When the bus is free, both lines are HIGH. The output stages of ISL6329 have an open drain/open collector in order to perform the wired-AND function. Data on the I<sup>2</sup>C bus can be transferred up to 100Kbps in the standard-mode or up to 400Kbps in the fast-mode. The level of logic "0" and logic "1" is dependent on associated value of V<sub>DD</sub> as per the "Electrical Specifications" table. One clock pulse is generated for each data bit transferred. The ISL6329 is a "SLAVE only" device, so the SCL line must always be controlled by an external master.

It is important to note that the I<sup>2</sup>C interface of the ISL6329 only works once the voltage on the VCC pin has risen above the POR rising threshold. The I<sup>2</sup>C will continue to remain active until the voltage on the VCC pin falls back below the falling POR threshold level. All registers are reset on POR.

### Data Validity

The data on the SDA line must be stable during the HIGH period of the SCL, unless generating a START or STOP condition. The HIGH or LOW state of the data line can only change when the clock signal on the SCL line is LOW. Refer to Figure 15.

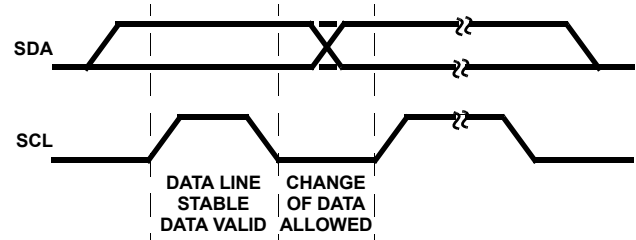


FIGURE 15. DATA VALIDITY

### START and STOP Conditions

Figure 16 shows a START (S) condition is a HIGH to LOW transition of the SDA line while SCL is HIGH.

The STOP (P) condition is a LOW to HIGH transition on the SDA line while SCL is HIGH. A STOP condition must be sent before each START condition.

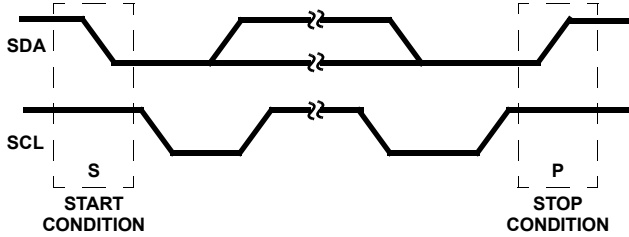


FIGURE 16. START AND STOP WAVEFORMS

**Byte Format**

Every byte put on the SDA line must be eight bits long. The number of bytes that can be transmitted per transfer is unrestricted. Each byte has to be followed by an acknowledge bit. Data is transferred with the most significant bit first (MSB) and the least significant bit last (LSB).

**Acknowledge**

Each address and data transmission uses 9-clock pulses. The ninth pulse is the acknowledge bit (A). After the start condition, the master sends 7 slave address bits and a R/W bit during the next 8-clock pulses. During the ninth clock pulse, the device that recognizes its own address holds the data line low to acknowledge. The acknowledge bit is also used by both the master and the slave to acknowledge receipt of register addresses and data as described in Figure 17.

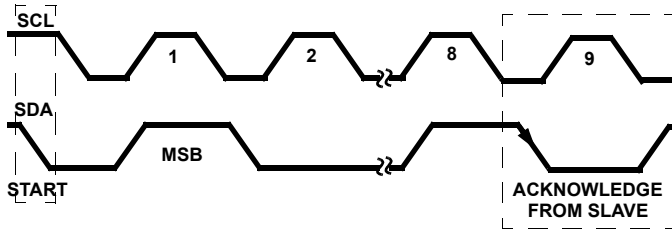


FIGURE 17. ACKNOWLEDGE ON THE I<sup>2</sup>C BUS

**ISL6329 I<sup>2</sup>C Slave Address**

All devices on the I<sup>2</sup>C bus must have a 7-Bit I<sup>2</sup>C address in order to be recognized. There are 8 selectable address available with the ISL6329. To program an address, a resistor must be tied from the I2C\_ADDR pin (Pin 52) to either ground or VCC. The resistor value will determine the address.

TABLE 4. I<sup>2</sup>C ADDRESS PROGRAMMING

RESISTOR TIED TO	RESISTOR VALUE	ADDRESS
Ground	0Ω	1000_110
Ground	20kΩ	1010_110
Ground	50kΩ	1001_110
Ground	100kΩ	1011_110
VCC	0Ω	1010_111
VCC	20kΩ	1010_111

TABLE 4. I<sup>2</sup>C ADDRESS PROGRAMMING (Continued)

RESISTOR TIED TO	RESISTOR VALUE	ADDRESS
VCC	50kΩ	1011_110
VCC	100kΩ	1011_111

**Communicating Over the I<sup>2</sup>C Bus**

Two transactions are supported on the I<sup>2</sup>C interface:

1. Write register
2. Read register from current address.

All transactions start with a control byte sent from the I<sup>2</sup>C master device. The control byte begins with a Start condition, followed by 7-bits of slave address. The last bit sent by the master is the R/W bit and is 0 for a write or 1 for a read. If any slaves on the I<sup>2</sup>C bus recognize their address, they will Acknowledge by pulling the serial data line low for the last clock cycle in the control byte. If no slaves exist at that address or are not ready to communicate, the data line will be 1, indicating a Not Acknowledge condition.

Once the control byte is sent, and the ISL6329 acknowledges it, the 2nd byte sent by the master must be a register address byte. This register address byte tells the ISL6329 which one of the internal registers it wants to write to or read from. The address of the first internal register, RGS0, is 0000\_0000. This register sets the Northbridge Offset, Overvoltage trip point and Power-good trip level. The address of the second internal register, RGS1, is 0000\_0001. This register sets the Core Offset, Overvoltage trip point and Power-good trip level. The address of the third register, RGS2, is 0000\_0010. The third register is for programming of the Power Savings Mode features. The fourth register, RGS3 (0000\_0011) is Reserved. The fifth register, RGS4 (0000\_0100), is for Phase Control and the GVOT voltage. The sixth register, RGS5 (0000\_0101), is used to set minimum phases for PSI and APD and has droop programmability. The seventh register, RGS6 (0000\_0110), controls the VID on the Fly slew rate, and various APA programming. It is important to note that RGS4, RGS5 and RGS6 can only be written to when the PWROK signal to the ISL6329 is low. Otherwise, once the ISL6329 receives a correct register address byte, it responds with an acknowledge.

TABLE 5. I<sup>2</sup>C REGISTER FUNCTIONS

REGISTER	ADDRESS	FUNCTIONS
RGS0	0000_0000	Northbridge DAC Offset, OVP, PGOOD
RGS1	0000_0001	Core DAC Offset, OVP, PGOOD
RGS2	0000_0010	PSI Mode Functions
RGS3	0000_0011	Reserved
RGS4	0000_0100	Phase Control and GVOT
RGS5	0000_0101	Min Num Phases and Droop Functions
RGS6	0000_0110	VOF Slew Rate and APA Functions

**Writing to the Internal Registers**

In order to change any of the operating parameters via the I<sup>2</sup>C bus, the internal registers must be written to. The five registers inside the ISL6329 can be written individually with separate write transactions or sequentially with one write transaction.



To write to a single register in the ISL6329, the master sends a control byte with the R/W bit set to 0, indicating a write. If it receives an Acknowledge from the ISL6329, it sends a register address byte representing the internal register to which it wants to write. The ISL6329 will respond with an Acknowledge. The master then sends a byte representing the data byte to be written into the desired register. The ISL6329 will respond with an Acknowledge. The master then issues a Stop condition, indicating to the ISL6329 that the current transaction is complete. Once this transaction completes, the ISL6329 will immediately update and change the operating parameters on-the-fly.

It is also possible to write to the all the registers sequentially. To do this the master must write to register RGS0 first. This transaction begins with the master sending a control byte with the R/W bit set to 0. If it receives an Acknowledge from the ISL6329, it sends the register address byte 0000\_0000, representing the internal register RGS0. The ISL6329 will respond with an Acknowledge. After sending the data byte to RGS0 and receiving an Acknowledge from the ISL6329, instead of sending a Stop condition, the master sends the data byte to be stored in register RGS1. After the ISL6329 responds with another Acknowledge, the master can either send a Stop condition to indicate that the current transaction is complete, or it can send the data byte to be stored in register RGS2. After the ISL6329 responds with an Acknowledge and if the PWROK signal is low, this process can continue with a byte being written to RGS4. Once the last register is written to, the ISL6329 will respond with an Acknowledge and the master would send a Stop condition, completing the transaction. Once this transaction completes the ISL6329 will immediately update and change the operating parameters on-the-fly.

### Reading from the Internal Registers

The ISL6329 has the ability to read from both registers separately or read from them consecutively. Prior to reading from an internal register, the master must first select the desired register by writing to it and sending the register's address byte. This process begins by the master sending a control byte with the R/W bit set to 0, indicating a write. Once it receives an Acknowledge from the ISL6329, it sends a register address byte representing the internal register it wants to read from (0000\_0000 for RGS1, 0000\_0001 for RGS2, etc). The ISL6329 will respond with an Acknowledge. The master must then respond with a Stop condition. After the Stop condition, the master follows with a new Start condition, and then sends a new control byte with the R/W bit set to 1, indicating a read. The ISL6329 will then respond by sending the master an Acknowledge, followed by the data byte stored in that register. The master must then send a Not Acknowledge followed by a Stop command, which will complete the read transaction.

It is also possible for all registers to be read consecutively. To do this the master must read from register RGS1 first. This transaction begins with the master sending a control byte with the R/W bit set to 0. If it receives an Acknowledge from the ISL6329, it sends the register address byte 0000\_0000, representing the internal register RGS1. The ISL6329 will respond with an Acknowledge. The master must then respond with a Stop condition. After the Stop condition the master follows with a new Start condition, and then sends a new control byte with the R/W bit set to 1, indicating a read. The ISL6329 will then respond by sending the master an Acknowledge, followed by the data byte stored in register RGS1. The master must then send an Acknowledge, and after doing so, the ISL6329 will respond by sending the data byte stored in register RGS2. The master must then send another Acknowledge, which the ISL6329 will respond to by sending the data byte stored in register RGS3. The master must then send a Not Acknowledge followed by a Stop command, which will complete the read transaction.

### Resetting the Internal Registers

The ISL6329's internal I<sup>2</sup>C registers always initialize to the states shown in Table 6 when the controller first receives power. Once the voltage on the VCC pin rises above the POR rising threshold level, these registers can be changed at any time via the I<sup>2</sup>C interface. If the voltage on the VCC pin falls below the POR falling threshold, the internal registers are automatically reset to their initial states.

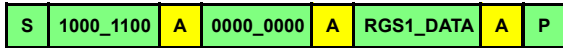
TABLE 6. I<sup>2</sup>C REGISTER INITIAL STATES

REGISTER	ADDRESS	INITIAL STATE
RGS0	0000_0000	0000_0000
RGS1	0000_0001	0000_0000
RGS2	0000_0010	0000_0001
RGS4	0000_0100	0111_1100
RGS5	0000_0101	0000_0000
RGS6	0000_0110	0010_0001

It is possible to reset the first three internal registers without powering down the controller and without requiring the controller to stop regulating and soft-start again. Simply write the initial states to the internal registers over the I<sup>2</sup>C interface. To initialize RGS4, PWROK must be low.

## I<sup>2</sup>C Read and Write Protocol

### WRITE TO A SINGLE REGISTER



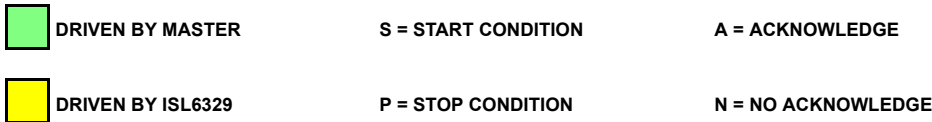
### WRITE TO ALL REGISTERS



### READ FROM SINGLE REGISTER



### READ FROM ALL REGISTERS



## Register Bit Definitions

The bits for RGS0 and RGS1 are utilized in the same manner by the ISL6329 (see Table 5). Bit-7 enables the overvoltage protection trip point to be increased. Bit-6 enables the Power-good trip point to be increased. These bits will be interpreted by the ISL6329 according to Table 7. Bits 5 through 0 determine the amount of offset for the particular regulator. See Table 8 for the bit codes and the corresponding offset voltages from the nominal DAC.

TABLE 7. BIT [7] AND [6] of REGISTER RGS0 AND RGS1

BIT 7	OVP TRIP LEVEL
0	1.8V or V <sub>DAC</sub> + 250mV, whichever is greater
1	1.8V or V <sub>DAC</sub> + 500mV, whichever is greater
BIT 6	PGOOD TRIP LEVEL
0	V <sub>DAC</sub> <sub>CORE</sub> +250mV/-300mV V <sub>DAC</sub> <sub>NB</sub> - 300mV
1	V <sub>DAC</sub> <sub>CORE</sub> +300mV/-350mV V <sub>DAC</sub> <sub>NB</sub> - 350mV

NOTE: All Pgood trip points have 50mV hysteresis

TABLE 8. BITS [5:0] REGISTER RGS0 and RGS1 (VOLTAGE MARGINING OFFSET)

BIT5	BIT4	BIT3	BIT2	BIT1	BIT0	V <sub>OFFSET</sub> (mV)
V05	V04	V03	V02	V01	V00	
1	0	0	0	0	0	-800
1	0	0	0	0	1	-775
1	0	0	0	1	0	-750
1	0	0	0	1	1	-725
1	0	0	1	0	0	-700
1	0	0	1	0	1	-675
1	0	0	1	1	0	-650

TABLE 8. BITS [5:0] REGISTER RGS0 and RGS1 (VOLTAGE MARGINING OFFSET) (Continued)

BIT5	BIT4	BIT3	BIT2	BIT1	BIT0	V <sub>OFFSET</sub> (mV)
V05	V04	V03	V02	V01	V00	
1	0	0	1	1	1	-625
1	0	1	0	0	0	-600
1	0	1	0	0	1	-575
1	0	1	0	1	0	-550
1	0	1	0	1	1	-525
1	0	1	1	0	0	-500
1	0	1	1	1	0	-475
1	0	1	1	1	1	-450
1	0	1	1	1	1	-425
1	1	0	0	0	0	-400
1	1	0	0	0	1	-375
1	1	0	0	1	0	-350
1	1	0	0	1	1	-325
1	1	0	1	0	0	-300
1	1	0	1	0	1	-275
1	1	0	1	1	0	-250
1	1	0	1	1	1	-225
1	1	1	0	0	0	-200
1	1	1	0	0	1	-175
1	1	1	0	1	0	-150
1	1	1	0	1	1	-125
1	1	1	1	0	0	-100
1	1	1	1	0	1	-75
1	1	1	1	1	0	-50

**TABLE 8. BITS [5:0] REGISTER RGS0 and RGS1 (VOLTAGE MARGINING OFFSET) (Continued)**

BIT5	BIT4	BIT3	BIT2	BIT1	BIT0	V <sub>OFFSET</sub> (mV)
VO5	VO4	VO3	VO2	VO1	VO0	
1	1	1	1	1	1	-25
0	0	0	0	0	0	0
0	0	0	0	0	1	25
0	0	0	0	1	0	50
0	0	0	0	1	1	75
0	0	0	1	0	0	100
0	0	0	1	0	1	125
0	0	0	1	1	0	150
0	0	0	1	1	1	175
0	0	1	0	0	0	200
0	0	1	0	0	1	225
0	0	1	0	1	0	250
0	0	1	0	1	1	275
0	0	1	1	0	0	300
0	0	1	1	0	1	325
0	0	1	1	1	0	350
0	0	1	1	1	1	375
0	1	0	0	0	0	400
0	1	0	0	0	1	425
0	1	0	0	1	0	450
0	1	0	0	1	1	475
0	1	0	1	0	0	500
0	1	0	1	0	1	525
0	1	0	1	1	0	550
0	1	0	1	1	1	575
0	1	1	0	0	0	600
0	1	1	0	0	1	625
0	1	1	0	1	0	650
0	1	1	0	1	1	675
0	1	1	1	0	0	700
0	1	1	1	0	1	725
0	1	1	1	1	0	750
0	1	1	1	1	1	775

The bits for Register RGS2 control some of the functionality of the ISL6329 for Power Savings Mode. Bit0 selects whether diode emulation is enabled in Power Savings Mode. Bits 1 and 2 control the number of PWM cycles between adding of phases when exiting Power Savings Mode. Bits 3 and 4 control the number of PWM cycles between dropping of phases when entering Power Savings Mode. Bit 5 will disable/enable the DAC offset when in Power Savings Mode. Bits 6 and 7 are reserved.

See Table 9 for a complete description of register RGS2 bits and their functionality.

**TABLE 9. BITS [7:0] REGISTER RGS2**

Bits [7:6]	Reserved
<b>Bit 5</b>	<b>Offset Enable in Power Savings Mode</b>
0	ENABLED (Default)
1	DISABLED
<b>Bits [4:3]</b>	<b>Number of PWM Cycles Between Dropping Phases</b>
00	1 PWM Cycle (default)
01	2 PWM Cycles
10	4 PWM Cycles
11	0 PWM Cycles (All Phases Drop at Once)
<b>Bits [2:1]</b>	<b>Number of PWM Cycles Between Adding Phases</b>
00	1 PWM Cycle (Default)
01	2 PWM Cycles
10	4 PWM Cycles
11	0 PWM Cycles (All Phases Added at Once)
<b>Bit 0</b>	<b>Diode Emulation in Power Savings Mode</b>
0	Disabled
1	Enabled (Default)

Register RGS4 controls the number of active phases and the GVOT level. It can only be written to when the PWROK signal is low. Bit 7 is reserved. Bits 6 through 2 control the number of active phases. It is important to note that if a bit is set to 1 then all the lesser significant bits must also be set to 1 as well. Bits 1 and 0 control the GVOT voltage level. This register can only be written to when PWROK is LOW.

**TABLE 10. BITS [7:0] REGISTER RGS4**

Bit 7	Reserved
<b>Bits [6:2]</b>	<b>Active Phase Control</b>
00000	Single Phase Regulator
00001	Two Phase Regulator
00011	Three Phase Regulator
00111	Four Phase Regulator
01111	Five Phase Regulator
11111	Six Phase Regulator (Default)
<b>Bits [1:0]</b>	<b>GVOT Level</b>
00	5.75V (Default)
01	6.75V
10	7.75V
11	11.2V

The bits for Register RGS5 control some of the functionality of the ISL6329 for Power Savings Mode, Droop Gain, NB Droop

Control. Bits 0 and 1 are for overriding analog programming of NB droop control. Bits 2 and 3 are for adjusting the droop gain. Bits 4 and 5 override the analog programming for number of active phases in Power Savings Mode. This register can only be written to when PWROK is LOW.

TABLE 11. BITS [7:0] REGISTER RGS5

Bits [7:6]	Reserved
Bits [5:4]	Number of Active Phases in Power Savings Mode
0x	No Action (Default)
10	Num Phases in PSI = 1
11	Num Phases in PSI = 2
Bits [3:2]	Core Droop Gain Adjust
00	Droop Current Gain = 1 (Default)
01	Droop Disabled
10	Droop Current Gain = 1/2
11	Droop Current Gain = 1/4
Bits [1:0]	Northbridge Droop Control Override
0x	No Action (Default)
10	Northbridge Droop Disabled
11	Northbridge Droop Enabled

The bits for Register RGS6 control some of the functionality of the ISL6329 for VID on the Fly Slew Rate and APA. Bits 0 through 3 are reserved. Bit 4 selects whether APA is controlled by monitoring the VSEN pin or the COMP pin. Bit 5 will disable/enable APAL and APAH events. Bits 6 and 7 control the VID on the Fly slew rate. This register can only be written to when PWROK is Low.

TABLE 12. BITS [7:0] REGISTER RGS6

Bits [7:6]	VID on the Fly Slew Rate
00	2.8mV/μsec
01	5.6mV/μsec
10	7.5mV/μsec
11	9.4mV/μsec
Bit 5	Enable APAL and APAH Events
0	Disabled
1	ENABLED (Default)
Bit 4	VSEN or COMP APA Monitoring
0	Monitor VSEN (Default)
1	Monitor COMP
Bits [3:0]	Reserved

## General Design Guide

This design guide is intended to provide a high-level explanation of the steps necessary to create a multiphase power converter. It is assumed that the reader is familiar with many of the basic skills and

techniques referenced below. In addition to this guide, Intersil provides complete reference designs that include schematics, bills of materials, and example board layouts for all common microprocessor applications.

## Power Stages

The first step in designing a multiphase converter is to determine the number of phases. This determination depends heavily on the cost analysis which in turn depends on system constraints that differ from one design to the next. Principally, the designer will be concerned with whether components can be mounted on both sides of the circuit board, whether through-hole components are permitted, the total board space available for power-supply circuitry, and the maximum amount of load current. Generally speaking, the most economical solutions are those in which each phase handles between 25A and 30A. All surface-mount designs will tend toward the lower end of this current range. If through-hole MOSFETs and inductors can be used, higher per-phase currents are possible. In cases where board space is the limiting constraint, current can be pushed as high as 40A per phase, but these designs require heat sinks and forced air to cool the MOSFETs, inductors and heat-dissipating surfaces.

## MOSFETS

The choice of MOSFETs depends on the current each MOSFET will be required to conduct, the switching frequency, the capability of the MOSFETs to dissipate heat, and the availability and nature of heat sinking and air flow.

## LOWER MOSFET POWER CALCULATION

The calculation for power loss in the lower MOSFET is simple, since virtually all of the loss in the lower MOSFET is due to current conducted through the channel resistance ( $r_{DS(ON)}$ ). In Equation 23,  $I_M$  is the maximum continuous output current,  $I_{PP}$  is the peak-to-peak inductor current (see Equation 2), and  $d$  is the duty cycle ( $V_{OUT}/V_{IN}$ ).

$$P_{LOW,1} = r_{DS(ON)} \cdot \left[ \left( \frac{I_M}{N} \right)^2 \cdot (1-d) + \frac{I_{L,PP}^2 \cdot (1-d)}{12} \right] \quad (\text{EQ. 23})$$

An additional term can be added to the lower-MOSFET loss equation to account for additional loss accrued during the dead time when inductor current is flowing through the lower-MOSFET body diode. This term is dependent on the diode forward voltage at  $I_M$ ,  $V_{D(ON)}$ , the switching frequency,  $f_S$ , and the length of dead times,  $t_{d1}$  and  $t_{d2}$ , at the beginning and the end of the lower-MOSFET conduction interval respectively.

$$P_{LOW,2} = V_{D(ON)} \cdot f_S \cdot \left[ \left( \frac{I_M}{N} + \frac{I_{PP}}{2} \right) \cdot t_{d1} + \left( \frac{I_M}{N} - \frac{I_{PP}}{2} \right) \cdot t_{d2} \right] \quad (\text{EQ. 24})$$

The total maximum power dissipated in each lower MOSFET is approximated by the summation of  $P_{LOW,1}$  and  $P_{LOW,2}$ .

## UPPER MOSFET POWER CALCULATION

In addition to  $r_{DS(ON)}$  losses, a large portion of the upper-MOSFET losses are due to currents conducted across the input voltage ( $V_{IN}$ ) during switching. Since a substantially higher portion of the upper-MOSFET losses are dependent on switching frequency, the power calculation is more complex. Upper MOSFET losses can be

divided into separate components involving the upper-MOSFET switching times, the lower-MOSFET body-diode reverse-recovery charge,  $Q_{rr}$ , and the upper MOSFET  $r_{DS(ON)}$  conduction loss.

When the upper MOSFET turns off, the lower MOSFET does not conduct any portion of the inductor current until the voltage at the phase node falls below ground. Once the lower MOSFET begins conducting, the current in the upper MOSFET falls to zero as the current in the lower MOSFET ramps up to assume the full inductor current. In Equation 25, the required time for this commutation is  $t_1$  and the approximated associated power loss is  $P_{UP,1}$ .

$$P_{UP,1} \approx V_{IN} \cdot \left( \frac{I_M}{N} + \frac{I_{PP}}{2} \right) \cdot \left( \frac{t_1}{2} \right) \cdot f_S \quad (\text{EQ. 25})$$

At turn on, the upper MOSFET begins to conduct and this transition occurs over a time  $t_2$ . In Equation 26, the approximate power loss is  $P_{UP,2}$ .

$$P_{UP,2} \approx V_{IN} \cdot \left( \frac{I_M}{N} - \frac{I_{PP}}{2} \right) \cdot \left( \frac{t_2}{2} \right) \cdot f_S \quad (\text{EQ. 26})$$

A third component involves the lower MOSFET reverse-recovery charge,  $Q_{rr}$ . Since the inductor current has fully commutated to the upper MOSFET before the lower-MOSFET body diode can recover all of  $Q_{rr}$ , it is conducted through the upper MOSFET across  $V_{IN}$ . The power dissipated as a result is  $P_{UP,3}$ .

$$P_{UP,3} = V_{IN} \cdot Q_{rr} \cdot f_S \quad (\text{EQ. 27})$$

Finally, the resistive part of the upper MOSFET is given in Equation 28 as  $P_{UP,4}$ .

$$P_{UP,4} \approx r_{DS(ON)} \cdot \left[ \left( \frac{I_M}{N} \right)^2 \cdot d + \frac{I_{PP}^2}{12} \right] \quad (\text{EQ. 28})$$

The total power dissipated by the upper MOSFET at full load can now be approximated as the summation of the results from Equations 25, 26, 27 and 28. Since the power equations depend on MOSFET parameters, choosing the correct MOSFETs can be an iterative process involving repetitive solutions to the loss equations for different MOSFETs and different switching frequencies.

## Internal Bootstrap Device

All three integrated drivers feature an internal bootstrap schottky diode. Simply adding an external capacitor across the BOOT and PHASE pins completes the bootstrap circuit. The bootstrap function is also designed to prevent the bootstrap capacitor from overcharging due to the large negative swing at the PHASE node. This reduces voltage stress on the boot to phase pins.

The bootstrap capacitor must have a maximum voltage rating above  $PVCC + 4V$  and its capacitance value can be chosen from Equation 29:

$$C_{BOOT\_CAP} \geq \frac{Q_{GATE}}{\Delta V_{BOOT\_CAP}} \quad (\text{EQ. 29})$$

$$Q_{GATE} = \frac{Q_{G1} \cdot PVCC}{V_{GS1}} \cdot N_{Q1}$$

where  $Q_{G1}$  is the amount of gate charge per upper MOSFET at  $V_{GS1}$  gate-source voltage and  $N_{Q1}$  is the number of control

MOSFETs. The  $\Delta V_{BOOT\_CAP}$  term is defined as the allowable droop in the rail of the upper gate drive.

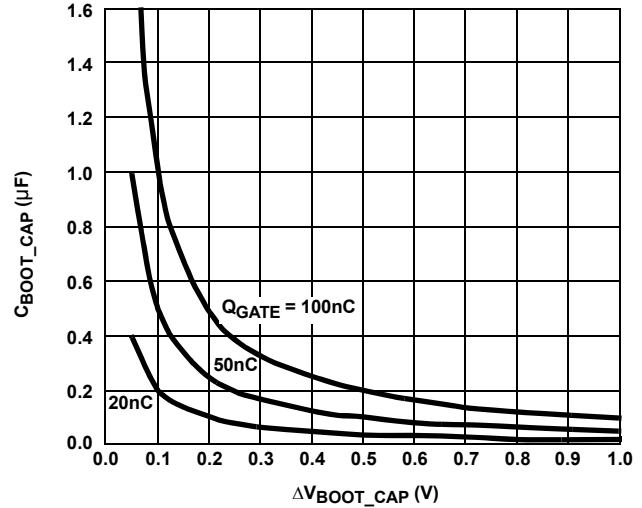


FIGURE 18. BOOTSTRAP CAPACITANCE vs BOOT RIPPLE VOLTAGE

## Gate Drive Voltage Versatility

The ISL6329 provides the user flexibility in choosing the gate drive voltage for efficiency optimization. The controller ties the upper and lower drive rails together. Simply applying a voltage from 5V up to 12V on  $PVCC$  sets both gate drive rail voltages simultaneously.

## Package Power Dissipation

When choosing MOSFETs, it is important to consider the amount of power being dissipated in the integrated drivers located in the controller. Since there are a total of three drivers in the controller package, the total power dissipated by all three drivers must be less than the maximum allowable power dissipation for the QFN package.

Calculating the power dissipation in the drivers for a desired application is critical to ensure safe operation. Exceeding the maximum allowable power dissipation level will push the IC beyond the maximum recommended operating junction temperature of  $+125^{\circ}\text{C}$ . The maximum allowable IC power dissipation for the 7x7 QFN package is approximately 3.5W at room temperature. See “Layout Considerations” on page 34 for thermal transfer improvement suggestions.

When designing the ISL6329 into an application, it is recommended that the following calculation is used to ensure safe operation at the desired frequency for the selected MOSFETs. The total gate drive power losses,  $P_{Qg\_TOT}$ , due to the gate charge of MOSFETs and the integrated driver's internal circuitry and their corresponding average driver current can be estimated with Equations 30 and 31, respectively.

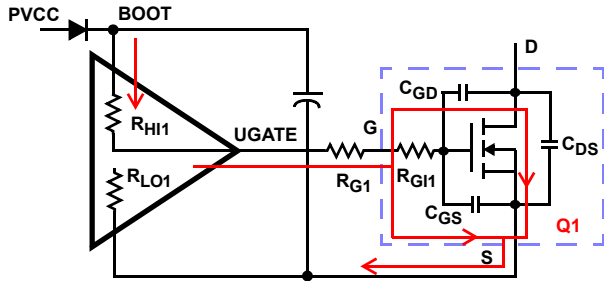
$$P_{Qg\_TOT} = P_{Qg\_Q1} + P_{Qg\_Q2} + I_Q \cdot VCC$$

$$P_{Qg\_Q1} = \frac{3}{2} \cdot Q_{G1} \cdot PVCC \cdot F_{SW} \cdot N_{Q1} \cdot N_{PHASE} \quad (\text{EQ. 30})$$

$$P_{Qg\_Q2} = Q_{G2} \cdot PVCC \cdot F_{SW} \cdot N_{Q2} \cdot N_{PHASE}$$

$$I_{DR} = \left( \frac{3}{2} \cdot Q_{G1} \cdot N_{Q1} + Q_{G2} \cdot N_{Q2} \right) \cdot N_{PHASE} \cdot F_{SW} + I_Q \quad (\text{EQ. 31})$$

In Equations 30 and 31,  $P_{Qg\_Q1}$  is the total upper gate drive power loss and  $P_{Qg\_Q2}$  is the total lower gate drive power loss; the gate charge ( $Q_{G1}$  and  $Q_{G2}$ ) is defined at the particular gate to source drive voltage  $V_{CC}$  in the corresponding MOSFET data sheet;  $I_Q$  is the driver total quiescent current with no load at both drive outputs;  $N_{Q1}$  and  $N_{Q2}$  are the number of upper and lower MOSFETs per phase, respectively;  $N_{PHASE}$  is the number of active phases. The  $I_Q \cdot V_{CC}$  product is the quiescent power of the controller without capacitive load and is typically 75mW at 300kHz.



PHASE  
FIGURE 19. TYPICAL UPPER-GATE DRIVE TURN-ON PATH

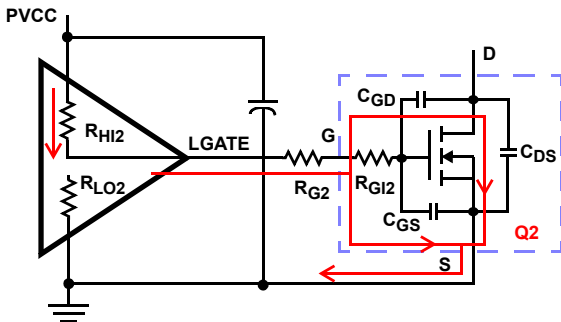


FIGURE 20. TYPICAL LOWER-GATE DRIVE TURN-ON PATH

The total gate drive power losses are dissipated among the resistive components along the transition path and in the bootstrap diode. The portion of the total power dissipated in the controller itself is the power dissipated in the upper drive path resistance ( $P_{DR\_UP}$ ), the lower drive path resistance ( $P_{DR\_LOW}$ ), and in the boot strap diode ( $P_{BOOT}$ ). The rest of the power will be dissipated by the external gate resistors ( $R_{G1}$  and  $R_{G2}$ ) and the internal gate resistors ( $R_{G11}$  and  $R_{G12}$ ) of the MOSFETs. Figures 19 and 20 show the typical upper and lower gate drives turn-on transition path. The total power dissipation in the controller itself,  $P_{DR}$ , can be roughly estimated as:

$$P_{DR} = P_{DR\_UP} + P_{DR\_LOW} + P_{BOOT} + (I_Q \cdot V_{CC})$$

$$P_{BOOT} = \frac{P_{Qg\_Q1}}{3}$$

$$P_{DR\_UP} = \left( \frac{R_{HI1}}{R_{HI1} + R_{EXT1}} + \frac{R_{LO1}}{R_{LO1} + R_{EXT1}} \right) \cdot \frac{P_{Qg\_Q1}}{3} \quad (EQ. 32)$$

$$P_{DR\_LOW} = \left( \frac{R_{HI2}}{R_{HI2} + R_{EXT2}} + \frac{R_{LO2}}{R_{LO2} + R_{EXT2}} \right) \cdot \frac{P_{Qg\_Q2}}{2}$$

$$R_{EXT1} = R_{G1} + \frac{R_{G11}}{N_{Q1}} \quad R_{EXT2} = R_{G2} + \frac{R_{G12}}{N_{Q2}}$$

## Inductor DCR Current Sensing Component Fine Tuning

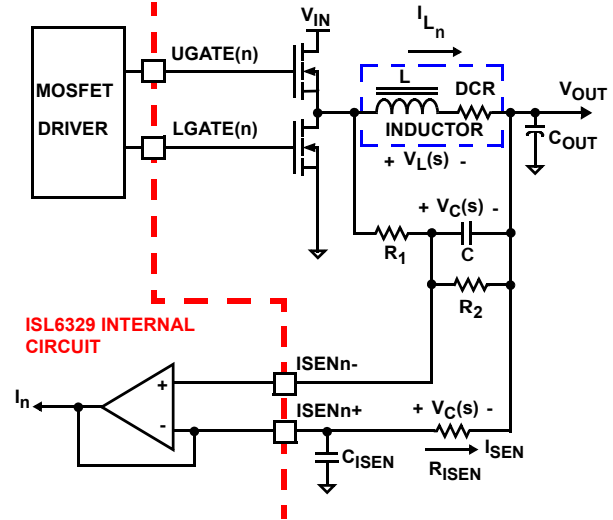


FIGURE 21. DCR SENSING CONFIGURATION

Due to errors in the inductance and/or DCR, it may be necessary to adjust the value of  $R_1$  and  $R_2$  to match the time constants correctly. The effects of time constant mismatch can be seen in the form of droop overshoot or undershoot during the initial load transient spike, as shown in Figure 22. Follow the steps below to ensure the R-C and inductor L/DCR time constants are matched accurately.

1. If the regulator is not utilizing droop, modify the circuit by placing the frequency set resistor between FS and Ground for the duration of this procedure.
2. Capture a transient event with the oscilloscope set to about  $L/DCR/2$  (sec/div). For example, with  $L = 1\mu H$  and  $DCR = 1m\Omega$ , set the oscilloscope to 500 $\mu s$ /div.
3. Record  $\Delta V_1$  and  $\Delta V_2$  as shown in Figure 22.

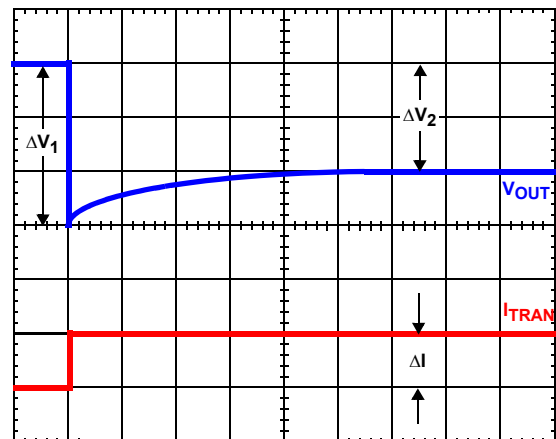


FIGURE 22. TIME CONSTANT MISMATCH BEHAVIOR

4. Select new values,  $R_{1,NEW}$  and  $R_{2,NEW}$ , for the time constant resistors based on the original values,  $R_{1,OLD}$  and  $R_{2,OLD}$ , using Equations 33 and 34.

$$R_{1,NEW} = R_{1,OLD} \cdot \frac{DV_1}{DV_2} \quad (\text{EQ. 33})$$

$$R_{2,NEW} = R_{2,OLD} \cdot \frac{DV_1}{DV_2} \quad (\text{EQ. 34})$$

5. Replace  $R_1$  and  $R_2$  with the new values and check to see that the error is corrected. Repeat the procedure if necessary.

## Loadline Regulation Resistor

The loadline regulation resistor, labeled  $R_{FB}$  in Figure 8, sets the desired loadline required for the application. Equation 35 can be used to calculate  $R_{FB}$ .

$$R_{FB} = \frac{V_{DROOP\_MAX}}{\left( \frac{I_{OUT\_MAX}}{N} \cdot DCR \right) \cdot \frac{1}{R_{ISEN}}} \cdot K \quad (\text{EQ. 35})$$

If no loadline regulation is required, the DRPCTRL pin can be used to enable or disable droop on the Core and Northbridge regulators independently. To choose the value for  $R_{FB}$  with no loadline, please refer to “Compensation Without Loadline Regulation” on page 31.

## Compensation With Loadline Regulation

The load-line regulated converter behaves in a similar manner to a peak current mode controller because the two poles at the output filter L-C resonant frequency split with the introduction of current information into the control loop. The final location of these poles is determined by the system function, the gain of the current signal, and the value of the compensation components,  $R_C$  and  $C_C$ .

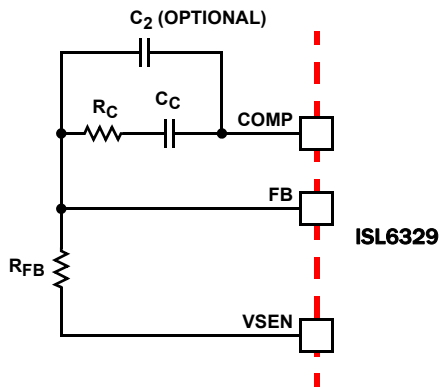


FIGURE 23. COMPENSATION CONFIGURATION FOR LOAD-LINE REGULATED ISL6329 CIRCUIT

Since the system poles and zero are affected by the values of the components that are meant to compensate them, the solution to the system equation becomes fairly complicated. Fortunately, there is a simple approximation that comes very close to an optimal solution. Treating the system as though it were a voltage-mode regulator, by compensating the L-C poles and the ESR zero

of the voltage mode approximation, yields a solution that is always stable with very close to ideal transient performance.

Select a target bandwidth for the compensated system,  $f_0$ . The target bandwidth must be large enough to assure adequate transient performance, but smaller than 1/3 of the per-channel switching frequency. The values of the compensation components depend on the relationships of  $f_0$  to the L-C pole frequency and the ESR zero frequency. For each of the following three, there is a separate set of equations for the compensation components.

In Equation 36, L is the per-channel filter inductance divided by the number of active channels; C is the sum total of all output capacitors; ESR is the equivalent series resistance of the bulk output filter capacitance; and  $V_{PP}$  is the peak-to-peak sawtooth signal amplitude as described in the “Electrical Specifications” on page 9.

Once selected, the compensation values in Equation 36 assure a stable converter with reasonable transient performance. In most cases, transient performance can be improved by making adjustments to  $R_C$ . Slowly increase the value of  $R_C$  while observing the transient performance on an oscilloscope until no further improvement is noted. Normally,  $C_C$  will not need adjustment. Keep the value of  $C_C$  from Equation 36 unless some performance issue is noted.

The optional capacitor,  $C_2$ , is sometimes needed to bypass noise away from the PWM comparator (see Figure 23). Keep a position available for  $C_2$ , and be prepared to install a high-frequency capacitor of between 22pF and 150pF in case any leading edge jitter problem is noted.

$$\text{Case 1: } \frac{1}{2 \cdot \pi \cdot \sqrt{L \cdot C}} > f_0$$

$$R_C = R_{FB} \cdot \frac{2 \cdot \pi \cdot f_0 \cdot V_{PP} \cdot \sqrt{L \cdot C}}{0.66 \cdot V_{IN}}$$

$$C_C = \frac{0.66 \cdot V_{IN}}{2 \cdot \pi \cdot V_{PP} \cdot R_{FB} \cdot f_0}$$

$$\text{Case 2: } \frac{1}{2 \cdot \pi \cdot \sqrt{L \cdot C}} \leq f_0 < \frac{1}{2 \cdot \pi \cdot C \cdot \text{ESR}}$$

$$R_C = R_{FB} \cdot \frac{V_{PP} \cdot (2 \cdot \pi)^2 \cdot f_0^2 \cdot L \cdot C}{0.66 \cdot V_{IN}} \quad (\text{EQ. 36})$$

$$C_C = \frac{0.66 \cdot V_{IN}}{(2 \cdot \pi)^2 \cdot f_0^2 \cdot V_{PP} \cdot R_{FB} \cdot \sqrt{L \cdot C}}$$

$$\text{Case 3: } f_0 > \frac{1}{2 \cdot \pi \cdot C \cdot \text{ESR}}$$

$$R_C = R_{FB} \cdot \frac{2 \cdot \pi \cdot f_0 \cdot V_{PP} \cdot L}{0.66 \cdot V_{IN} \cdot \text{ESR}}$$

$$C_C = \frac{0.66 \cdot V_{IN} \cdot \text{ESR} \cdot \sqrt{C}}{2 \cdot \pi \cdot V_{PP} \cdot R_{FB} \cdot f_0 \cdot \sqrt{L}}$$

## Compensation Without Loadline Regulation

The non load-line regulated converter is accurately modeled as a voltage-mode regulator with two poles at the L-C resonant

frequency and a zero at the ESR frequency. A type III controller, as shown in Figure 24, provides the necessary compensation.

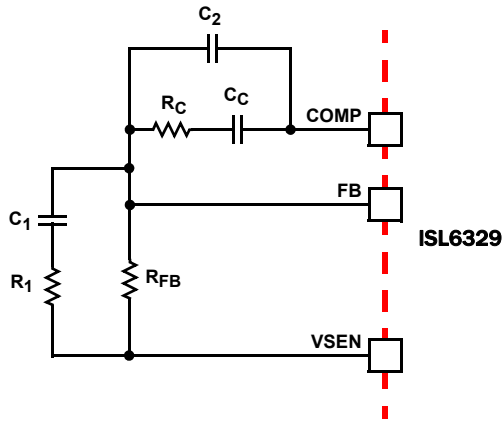


FIGURE 24. COMPENSATION CIRCUIT WITHOUT LOAD-LINE REGULATION

The first step is to choose the desired bandwidth,  $f_0$ , of the compensated system. Choose a frequency high enough to assure adequate transient performance but not higher than  $1/3$  of the switching frequency. The type-III compensator has an extra high-frequency pole,  $f_{HF}$ . This pole can be used for added noise rejection or to assure adequate attenuation at the error-amplifier high-order pole and zero frequencies. A good general rule is to choose  $f_{HF} = 10f_0$ , but it can be higher if desired. Choosing  $f_{HF}$  to be lower than  $10f_0$  can cause problems with too much phase shift below the system bandwidth.

$$R_1 = R_{FB} \cdot \frac{C \cdot ESR}{\sqrt{L \cdot C} - C \cdot ESR}$$

$$C_1 = \frac{\sqrt{L \cdot C} - C \cdot ESR}{R_{FB}}$$

$$C_2 = \frac{0.75 \cdot V_{IN}}{(2 \cdot \pi)^2 \cdot f_0 \cdot f_{HF} \cdot (\sqrt{L \cdot C}) \cdot R_{FB} \cdot V_{PP}} \quad (\text{EQ. 37})$$

$$R_C = \frac{V_{PP} \cdot (2\pi)^2 \cdot f_0 \cdot f_{HF} \cdot L \cdot C \cdot R_{FB}}{0.75 \cdot V_{IN} \cdot (2 \cdot \pi \cdot f_{HF} \cdot \sqrt{L \cdot C} - 1)}$$

$$C_C = \frac{0.75 \cdot V_{IN} \cdot (2 \cdot \pi \cdot f_{HF} \cdot \sqrt{L \cdot C} - 1)}{(2 \cdot \pi)^2 \cdot f_0 \cdot f_{HF} \cdot (\sqrt{L \cdot C}) \cdot R_{FB} \cdot V_{PP}}$$

In the solutions to the compensation equations, there is a single degree of freedom. For the solutions presented in Equation 38,  $R_{FB}$  is selected arbitrarily. The remaining compensation components are then selected according to Equation 38.

In Equation 38,  $L$  is the per-channel filter inductance divided by the number of active channels;  $C$  is the sum total of all output capacitors;  $ESR$  is the equivalent-series resistance of the bulk output-filter capacitance; and  $V_{PP}$  is the peak-to-peak sawtooth signal amplitude as described in "Electrical Specifications" on page 9.

$$\frac{1}{2 \cdot \pi \cdot \sqrt{L \cdot C}} > f_0$$

Case 1:

$$R_C = R_{FB} \cdot \frac{2 \cdot \pi \cdot f_0 \cdot V_{PP} \cdot \sqrt{L \cdot C}}{0.66 \cdot V_{IN}}$$

$$C_C = \frac{0.66 \cdot V_{IN}}{2 \cdot \pi \cdot V_{PP} \cdot R_{FB} \cdot f_0}$$

$$\frac{1}{2 \cdot \pi \cdot \sqrt{L \cdot C}} \leq f_0 < \frac{1}{2 \cdot \pi \cdot C \cdot ESR}$$

Case 2:

$$R_C = R_{FB} \cdot \frac{V_{PP} \cdot (2 \cdot \pi)^2 \cdot f_0^2 \cdot L \cdot C}{0.66 \cdot V_{IN}} \quad (\text{EQ. 38})$$

$$C_C = \frac{0.66 \cdot V_{IN}}{(2 \cdot \pi)^2 \cdot f_0^2 \cdot V_{PP} \cdot R_{FB} \cdot \sqrt{L \cdot C}}$$

$$f_0 > \frac{1}{2 \cdot \pi \cdot C \cdot ESR}$$

Case 3:

$$R_C = R_{FB} \cdot \frac{2 \cdot \pi \cdot f_0 \cdot V_{PP} \cdot L}{0.66 \cdot V_{IN} \cdot ESR}$$

$$C_C = \frac{0.66 \cdot V_{IN} \cdot ESR \cdot \sqrt{C}}{2 \cdot \pi \cdot V_{PP} \cdot R_{FB} \cdot f_0 \cdot \sqrt{L}}$$

## Output Filter Design

The output inductors and the output capacitor bank together to form a low-pass filter responsible for smoothing the pulsating voltage at the phase nodes. The output filter also must provide the transient energy until the regulator can respond. Because it has a low bandwidth compared to the switching frequency, the output filter limits the system transient response. The output capacitors must supply or sink load current while the current in the output inductors increases or decreases to meet the demand.

In high-speed converters, the output capacitor bank is usually the most costly (and often the largest) part of the circuit. Output filter design begins with minimizing the cost of this part of the circuit. The critical load parameters in choosing the output capacitors are the maximum size of the load step,  $\Delta I$ , the load-current slew rate,  $di/dt$ , and the maximum allowable output-voltage deviation under transient loading,  $\Delta V_{MAX}$ . Capacitors are characterized according to their capacitance, ESR, and ESL (equivalent series inductance).

At the beginning of the load transient, the output capacitors supply all of the transient current. The output voltage will initially deviate by an amount approximated by the voltage drop across the ESL. As the load current increases, the voltage drop across the ESR increases linearly until the load current reaches its final value. The capacitors selected must have sufficiently low ESL and ESR so that the total output-voltage deviation is less than the allowable maximum. Neglecting the contribution of inductor current and regulator response, the output voltage initially deviates by an amount:

$$\Delta V \approx ESL \cdot \frac{di}{dt} + ESR \cdot \Delta I \quad (\text{EQ. 39})$$

The filter capacitor must have sufficiently low ESL and ESR so that  $\Delta V < \Delta V_{MAX}$ .



Most capacitor solutions rely on a mixture of high frequency capacitors with relatively low capacitance in combination with bulk capacitors having high capacitance but limited high-frequency performance. Minimizing the ESL of the high-frequency capacitors allows them to support the output voltage as the current increases. Minimizing the ESR of the bulk capacitors allows them to supply the increased current with less output voltage deviation.

The ESR of the bulk capacitors also creates the majority of the output-voltage ripple. As the bulk capacitors sink and source the inductor AC ripple current (see “Interleaving” on page 12 and Equation 3), a voltage develops across the bulk capacitor ESR equal to  $I_{C,PP}(ESR)$ . Thus, once the output capacitors are selected, the maximum allowable ripple voltage,  $V_{PP(MAX)}$ , determines the lower limit on the inductance.

$$L \geq ESR \cdot \frac{(V_{IN} - N \cdot V_{OUT}) \cdot V_{OUT}}{f_S \cdot V_{IN} \cdot V_{PP(MAX)}} \quad (EQ. 40)$$

Since the capacitors are supplying a decreasing portion of the load current while the regulator recovers from the transient, the capacitor voltage becomes slightly depleted. The output inductors must be capable of assuming the entire load current before the output voltage decreases more than  $\Delta V_{MAX}$ . This places an upper limit on inductance.

Equation 41 gives the upper limit on L for the cases when the trailing edge of the current transient causes a greater output-voltage deviation than the leading edge. Equation 42 addresses the leading edge. Normally, the trailing edge dictates the selection of L because duty cycles are usually less than 50%. Nevertheless, both inequalities should be evaluated, and L should be selected based on the lower of the two results. In each equation, L is the per-channel inductance, C is the total output capacitance, and N is the number of active channels.

$$L \leq \frac{2 \cdot N \cdot C \cdot V_O}{(\Delta I)^2} \cdot [\Delta V_{MAX} - (\Delta I \cdot ESR)] \quad (EQ. 41)$$

$$L \leq \frac{1.25 \cdot N \cdot C}{(\Delta I)^2} \cdot [\Delta V_{MAX} - (\Delta I \cdot ESR)] \cdot (V_{IN} - V_O) \quad (EQ. 42)$$

### Switching Frequency

There are a number of variables to consider when choosing the switching frequency, as there are considerable effects on the upper MOSFET loss calculation. These effects are outlined in “MOSFETs” on page 28, and they establish the upper limit for the switching frequency. The lower limit is established by the requirement for fast transient response and small output-voltage ripple as outlined in “Output Filter Design” on page 32. Choose the lowest switching frequency that allows the regulator to meet the transient-response requirements.

Switching frequency is determined by the selection of the frequency-setting resistor,  $R_T$ . Figure 25 and Equation 43 are provided to assist in selecting the correct value for  $R_T$ .

$$R_T = 10^{[10.61 - (1.035 \cdot \log(f_S))]} \quad (EQ. 43)$$

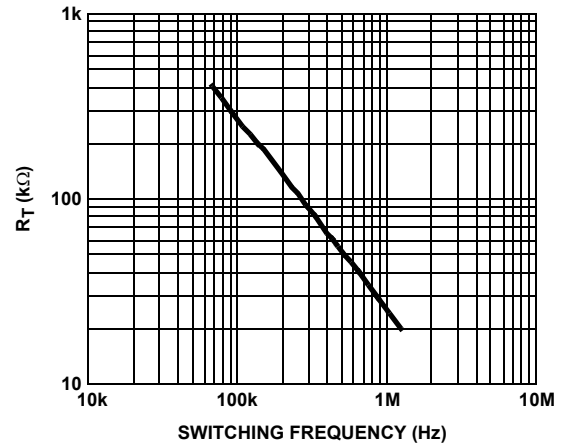


FIGURE 25.  $R_T$  vs SWITCHING FREQUENCY

### Input Capacitor Selection

The input capacitors are responsible for sourcing the AC component of the input current flowing into the upper MOSFETs. Their RMS current capacity must be sufficient to handle the AC component of the current drawn by the upper MOSFETs which is related to duty cycle and the number of active phases.

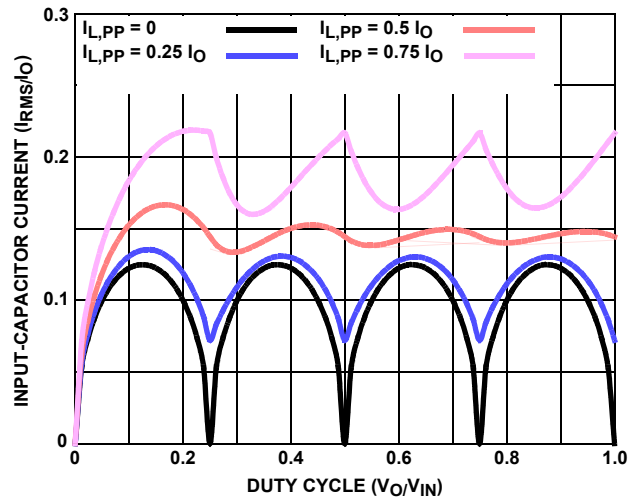


FIGURE 26. NORMALIZED INPUT-CAPACITOR RMS CURRENT vs DUTY CYCLE FOR 4-PHASE CONVERTER

For a four-phase design, use Figure 26 to determine the input-capacitor RMS current requirement set by the duty cycle, maximum sustained output current ( $I_O$ ), and the ratio of the peak-to-peak inductor current ( $I_{L,PP}$ ) to  $I_O$ . Select a bulk capacitor with a ripple current rating which will minimize the total number of input capacitors required to support the RMS current calculated.

The voltage rating of the capacitors should also be at least 1.25 times greater than the maximum input voltage. Figures 27 and 28 provide the same input RMS current information for three-phase and two-phase designs respectively. Use the same approach for selecting the bulk capacitor type and number.

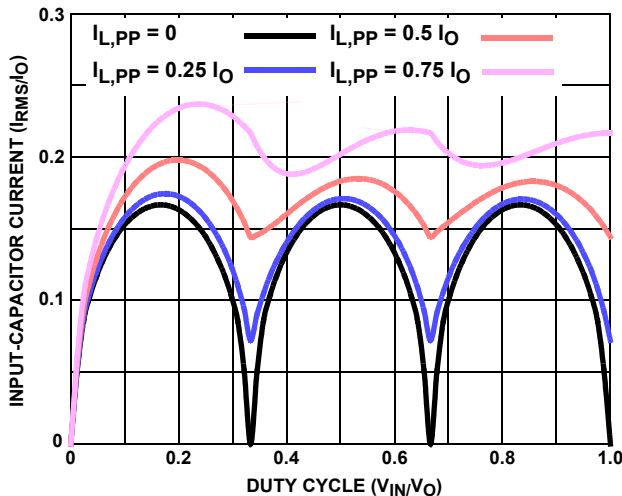


FIGURE 27. NORMALIZED INPUT-CAPACITOR RMS CURRENT FOR 3-PHASE CONVERTER

Low capacitance, high-frequency ceramic capacitors are needed in addition to the input bulk capacitors to suppress leading and falling edge voltage spikes. The spikes result from the high current slew rate produced by the upper MOSFET turn on and off. Select low ESL ceramic capacitors and place one as close as possible to each upper MOSFET drain to minimize board parasitics and maximize suppression.

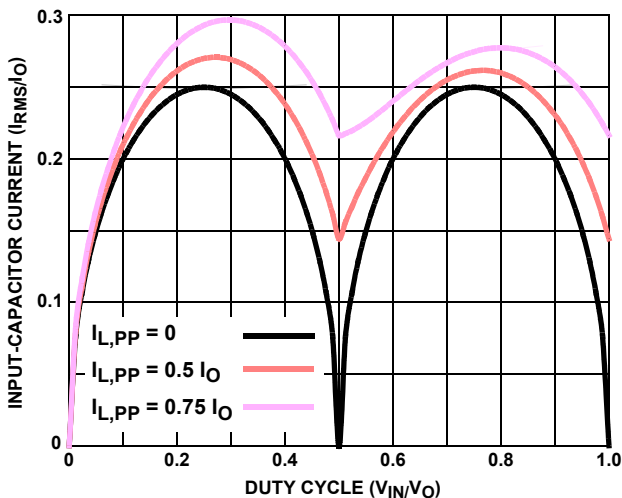


FIGURE 28. NORMALIZED INPUT-CAPACITOR RMS CURRENT FOR 2-PHASE CONVERTER

## Layout Considerations

MOSFETs switch very fast and efficiently. The speed with which the current transitions from one device to another causes voltage spikes across the interconnecting impedances and parasitic circuit elements. These voltage spikes can degrade efficiency, radiate noise into the circuit and lead to device overvoltage stress. Careful component selection, layout, and placement minimizes these voltage spikes. Consider, as an example, the turnoff transition of the upper PWM MOSFET. Prior to turnoff, the upper MOSFET was carrying channel current. During the turnoff, current stops flowing in the upper MOSFET and is picked up by the lower MOSFET. Any inductance in the switched current path generates a large voltage spike during the switching interval.

Careful component selection, tight layout of the critical components, and short, wide circuit traces minimize the magnitude of voltage spikes.

There are two sets of critical components in a DC/DC converter using a ISL6329 controller. The power components are the most critical because they switch large amounts of energy. Next are small signal components that connect to sensitive nodes or supply critical bypassing current and signal coupling.

The power components should be placed first, which include the MOSFETs, input and output capacitors, and the inductors. It is important to have a symmetrical layout for each power train, preferably with the controller located equidistant from each. Symmetrical layout allows heat to be dissipated equally across all power trains. Equidistant placement of the controller to the CORE and NB power trains it controls through the integrated drivers helps keep the gate drive traces equally short, resulting in equal trace impedances and similar drive capability of all sets of MOSFETs.

When placing the MOSFETs, try to keep the source of the upper FETs and the drain of the lower FETs as close as thermally possible. Input high-frequency capacitors,  $C_{HF}$ , should be placed close to the drain of the upper FETs and the source of the lower FETs. Input bulk capacitors,  $C_{BULK}$ , case size typically limits following the same rule as the high-frequency input capacitors. Place the input bulk capacitors as close to the drain of the upper FETs as possible and minimize the distance to the source of the lower FETs.

Locate the output inductors and output capacitors between the MOSFETs and the load. The high-frequency output decoupling capacitors (ceramic) should be placed as close as practicable to the decoupling target, making use of the shortest connection paths to any internal planes, such as vias to GND next or on the capacitor solder pad.

The critical small components include the bypass capacitors ( $C_{FILTER}$ ) for VCC and PVCC, and many of the components surrounding the controller including the feedback network and current sense components. Locate the VCC/PVCC bypass capacitors as close to the ISL6329 as possible. It is especially important to locate the components associated with the feedback circuit close to their respective controller pins, since they belong to a high-impedance circuit loop, sensitive to EMI pick-up.

A multi-layer printed circuit board is recommended. Figure 29 shows the connections of the critical components for the converter. Note that capacitors  $C_{IN}$  and  $C_{OUT}$  could each represent numerous physical capacitors. Dedicate one solid layer, usually the one underneath the component side of the board, for a ground plane and make all critical component ground connections with vias to this layer. Dedicate another solid layer as a power plane and break this plane into smaller islands of common voltage levels. Keep the metal runs from the PHASE terminal to output inductors short. The power plane should support the input power and output power nodes. Use copper filled polygons on the top and bottom circuit layers for the phase nodes. Use the remaining printed circuit layers for small signal wiring.

## **Routing UGATE, LGATE, and PHASE Traces**

Great attention should be paid to routing the UGATE, LGATE, and PHASE traces since they drive the power train MOSFETs using short, high current pulses. It is important to size them as large and as short as possible to reduce their overall impedance and inductance. They should be sized to carry at least one ampere of current (0.02" to 0.05"). Going between layers with vias should also be avoided, but if so, use two vias for interconnection when possible.

Extra care should be given to the LGATE traces in particular since keeping their impedance and inductance low helps to significantly reduce the possibility of shoot-through. It is also important to route each channels UGATE and PHASE traces in as close proximity as possible to reduce their inductances.

## **Current Sense Component Placement and Trace Routing**

One of the most critical aspects of the ISL6329 regulator layout is the placement of the inductor DCR current sense components and traces. The R-C current sense components must be placed as close to their respective ISEN+ and ISEN- pins on the ISL6329 as possible.

The sense traces that connect the R-C sense components to each side of the output inductors should be routed on the bottom of the board, away from the noisy switching components located on the top of the board. These traces should be routed side by side, and they should be very thin traces. It's important to route these traces as far away from any other noisy traces or planes as possible. These traces should pick up as little noise as possible.

## **Thermal Management**

For maximum thermal performance in high current, high switching frequency applications, connecting the thermal GND pad of the ISL6329 to the ground plane with multiple vias is recommended. This heat spreading allows the part to achieve its full thermal potential. It is also recommended that the controller be placed in a direct path of airflow if possible to help thermally manage the part.

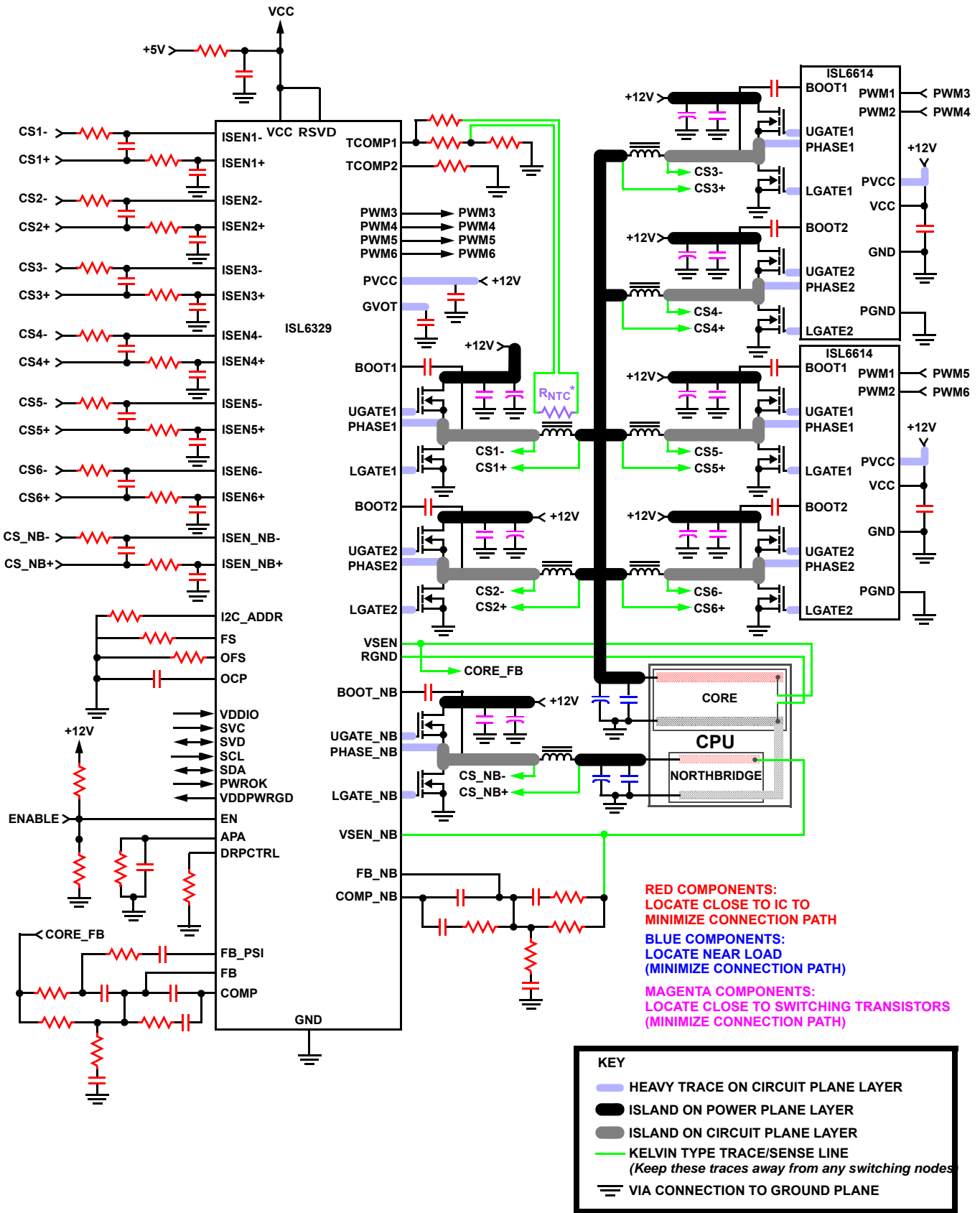


FIGURE 29. PRINTED CIRCUIT BOARD POWER PLANES AND ISLANDS

## Revision History

The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please go to web to make sure you have the latest Rev.

DATE	REVISION	CHANGE
4/19/11	FN7800.0	Initial release.

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\*For a complete listing of Applications, Related Documentation and Related Parts, please see the respective device information page on intersil.com: [ISL6329](http://www.intersil.com/ISL6329)

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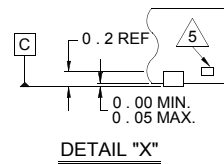
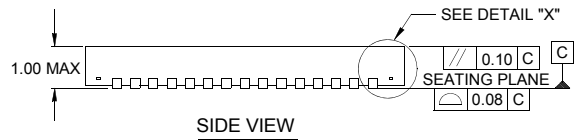
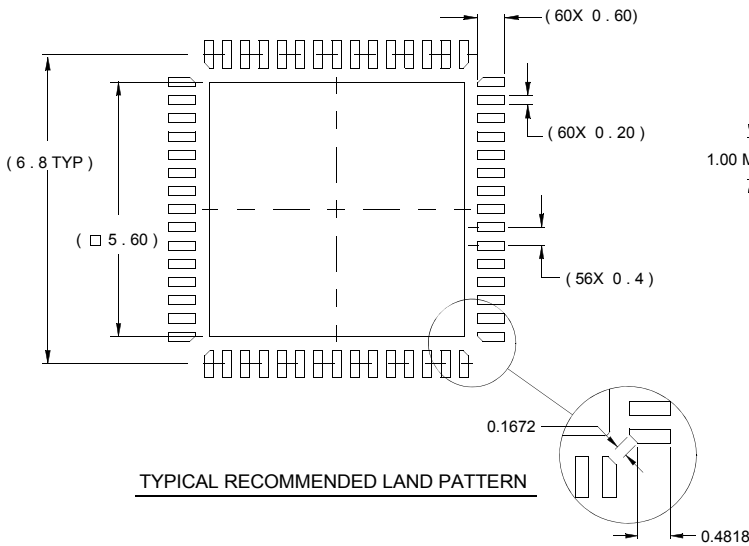
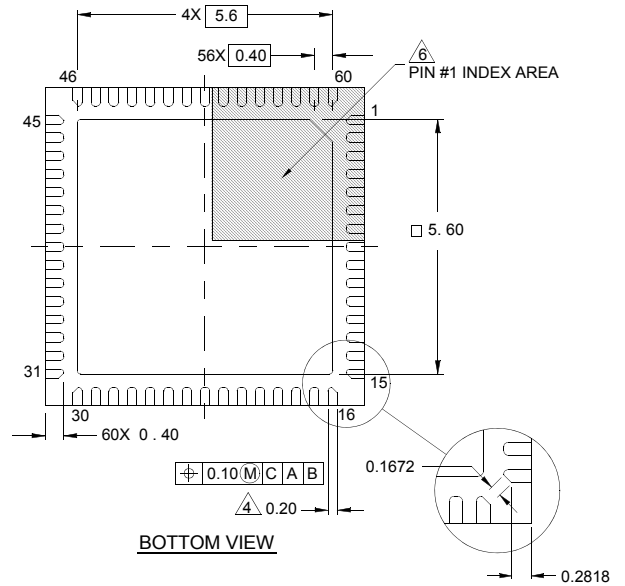
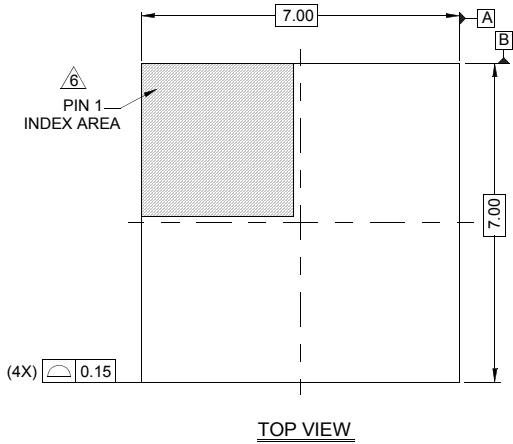
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# Package Outline Drawing

## L60.7x7

### 60 LEAD QUAD FLAT NO-LEAD PLASTIC PACKAGE

Rev 1, 2/10



**NOTES:**

1. Dimensions are in millimeters.  
Dimensions in ( ) for Reference Only.
2. Dimensioning and tolerancing conform to ASME Y14.5m-1994.
3. Unless otherwise specified, tolerance : Decimal  $\pm 0.10$   
Angular  $\pm 2.50^\circ$
4. Dimension applies to the metallized terminal and is measured between 0.015mm and 0.30mm from the terminal tip.
5. Tiebar shown (if present) is a non-functional feature.
6. The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.

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В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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